

# PCTEST ENGINEERING LABORATORY, INC.

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# **HEARING AID COMPATIBILITY**

Applicant Name:

Samsung Electronics Co., Ltd. 129, Samsung-ro, Maetan dong, Yeongtong-gu, Suwon-si Gyeonggi-do 16677, Korea Date of Testing: 04/29/2019 - 05/01/2019 Test Site/Location: PCTEST Lab, Columbia, MD, USA Test Report Serial No.: 1M1904030051-12-R1.A3L Date of Issue:

FCC ID: A3LSMA102U

APPLICANT: SAMSUNG ELECTRONICS CO., LTD.

Scope of Test: RF Emissions Testing

Application Type: Certification
FCC Rule Part(s): CFR §20.19(b)
HAC Standard: ANSI C63.19-2011

CTIA Test Plan for Hearing Aid Compatibility Rev 3.1.1, May 2017

285076 D01 HAC Guidance v05

285076 D02 T-Coil testing for CMRS IP v03

05/20/2019

**DUT Type:** Portable Handset **Model:** SM-A102U

Test Device Serial No.: Pre-Production Sample [S/N: 12726; 10223]

C63.19-2011 HAC Category: M3 (RF EMISSIONS CATEGORY)

Note: This revised Test Report (S/N: 1M1904030051-12-R1.A3L) supersedes and replaces the previously issued test report on the same subject device for the same type of testing as indicated. Please discard or destroy the previously issued test report(s) and dispose of it accordingly.

This wireless portable device has been shown to be hearing-aid compatible under the above rated category, specified in ANSI/IEEE Std. C63.19-2011 and has been tested in accordance with the specified measurement procedures. Hearing-Aid Compatibility is based on the assumption that all production units will be designed electrically identical to the device tested in this report. Test results reported herein relate only to the item(s) tested. North America bands only.

I attest to the accuracy of data. All measurements reported herein were performed by me or were made under my supervision and are correct to the best of my knowledge and belief. I assume full responsibility for the completeness of these measurements and vouch for the qualifications of all persons taking them.







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#### 1. INTRODUCTION

On July 10, 2003, the Federal Communications Commission (FCC) adopted new rules requiring wireless manufacturers and service providers to provide digital wireless phones that are compatible with hearing aids. The FCC has modified the exemption for wireless phones under the Hearing Aid Compatibility Act of 1998 (HAC Act) in WT Docket 01-309 RM-86581 to extend the benefits of wireless telecommunications to individuals with hearing disabilities. These benefits encompass business, social and emergency communications, which increase the value of the wireless network for everyone. An estimated more than 10% of the population in the United States show signs of hearing impairment and of that fraction, almost 80% use hearing aids. Approximately 500 million people worldwide suffer from hearing loss.

#### **Compatibility Tests Involved:**

The standard calls for wireless communications devices to be measured for:

- RF Electric-field emissions
- T-coil mode, magnetic-signal strength in the audio band
- T-coil mode, magnetic-signal frequency response through the audio band
- T-coil mode, magnetic-signal and noise articulation index

The hearing aid must be measured for:

- RF immunity in microphone mode
- RF immunity in T-coil mode

In the following tests and results, this report includes the evaluation for a wireless communications device.



Figure 1-1 Hearing Aid in-vitu

<sup>&</sup>lt;sup>1</sup> FCC Rule & Order, WT Docket 01-309 RM-8658

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#### 2. **DUT DESCRIPTION**



FCC ID: A3LSMA102U

Manufacturer: Samsung Electronics Co., Ltd.

129, Samsung-ro, Maetan dong,

Yeongtong-gu, Suwon-si Gyeonggi-do 16677, Korea

Model: SM-A102U Serial Number: 12726; 10223 Antenna Configurations: Internal Antenna DUT Type: Portable Handset

#### **Power Reduction for WIFI**

This device uses an independent fixed level power reduction mechanism for 2.4GHz, and 5GHz 20MHz and 40MHz operations during voice or VoIP held to ear scenarios. Reduced powers were used to evaluate for low-power exemption in Section 9.II for WIFI. Detailed descriptions of the power reduction mechanism are included in the operational description.

#### II. LTE Band Selection

This device supports the following pairs of LTE bands with similar frequencies: LTE B12 & B17, LTE B25 & B2, LTE B26 & B5, LTE B66 & B4, and LTE B38 & B41. These pairs of LTE bands have the same target power and shares the same transmission path. Since the supported frequency span for the smaller LTE bands are completely covered by the larger LTE bands, only the larger LTE bands (LTE B12, B25, B26, B66, and B41) were evaluated for hearing-aid compliance.

#### III. Device Serial Numbers

Several samples with identical hardware were used to support HAC testing. The manufacturer has confirmed that the device(s) tested have the same physical, mechanical, and thermal characteristics are within operational tolerances expected for production units. The serial numbers used for each test are indicated alongside the results in Section 11.

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#### Table 2-1 A3LSMA102U HAC Air Interfaces

			LONATOL	O HAO All lilleriaces	
Air-Interface	Band (MHz)	Type Transport	HAC Tested	Simultaneous But Not Tested	Name of Voice Service
	835	1/0	V	Vers MIEL en DT	CMDC Voice
CDMA	1900	VO	Yes	Yes: WIFI or BT	CMRS Voice
	EvDO	VD	No <sup>1</sup>	Yes: WIFI or BT	Google Duo
	850	VO	Yes	Yes: WIFI or BT	CMRS Voice
GSM	1900	VO	163	res. Will of Bi	CIVINS VOICE
	GPRS/EDGE	VD	No <sup>1</sup>	Yes: WIFI or BT	Google Duo
	850				
UMTS	1700	VD	No <sup>1</sup>	Yes: WIFI or BT	CMRS Voice
UIVITS	1900				
	HSPA	VD	No <sup>1</sup>	Yes: WIFI or BT	Google Duo
	680 (B71)		No <sup>1 2</sup>		
	700 (B12)				
	700 (B17)				
	780 (B13)				
790 (B	790 (B14)				
	850 (B5)				
LTE (FDD)	850 (B26)	VD Yes: WIFI or BT	VoLTE, Google Duo		
	1700 (B4)		No'		
	1700 (B66)				
	1900 (B2)				
	1900 (B25)				
	2300 (B30)				
	2500 (B7)				
LTE (TDD)	2600 (B38)	1/0	V	Very MUEL on DT	ValTE Canala Dua
LTE (TDD)	2600 (B41)	VD	Yes	Yes: WIFI or BT	VoLTE, Google Duo
	2450				
	5200 (U-NII 1)				
WIFI	5300 (U-NII 2A)	VD	No <sup>1</sup>	Yes: CDMA, GSM, UMTS, or LTE	VoWIFI, Google Duo
	5500 (U-NII 2C)				
	5800 (U-NII 3)				
ВТ	2450	DT	No	Yes: CDMA, GSM, UMTS, or LTE	N/A
Type Transport VO = Voice Only			Notes: 1. Evaluated fo	or MIF and low-power exemption.	

VO = Voice Only

DT = Digital Data - Not intended for Voice Services

VD = CMRS and/or IP Voice over Data Transport

1. Evaluated for MIF and low-power exemption.

2. LTE B71, while outside the scope of ANSI C63.19 and FCC HAC regulations, was additionally tested according to the existing HAC procedures with currently available test equipment.

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#### **ANSI/IEEE C63.19 PERFORMANCE CATEGORIES** 3.

#### I. RF EMISSIONS

The ANSI Standard presents performance requirements for acceptable interoperability of hearing aids with wireless communications devices. When these parameters are met, a hearing aid operates acceptably in close proximity to a wireless communications device.

Category	Telephone RF Parameters			
Near field Category	E-field emissions CW dB(V/m)			
	f < 960 MHz			
M1	50 to 55			
M2	45 to 50			
M3	40 to 45			
M4	< 40			
	f > 960 MHz			
M1	40 to 45			
M2	35 to 40			
М3	30 to 35			
M4	< 30			
Table 3-1 WD near-field categories as defined in ANSI C63.19-2011				

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#### SYSTEM SPECIFICATIONS 4.

#### **EF3DV3 E-Field Probe Description**

Construction: One dipole parallel, two dipoles normal to probe axis

Built-in shielding against static charges

Calibration: In air from 30 MHz to 6.0 GHz

(absolute accuracy ±5.1%, k=2)

30 MHz to > 6 GHz; Frequency:

Linearity: ± 0.2 dB (30 MHz to 6 GHz)

± 0.2 dB in air (rotation around probe axis) Directivity

± 0.4 dB in air (rotation normal to probe axis)

2 V/m to > 1000 V/m Dynamic Range

(M3 or better device readings fall well below diode

compression point)

Linearity: ± 0.2 dB

**Dimensions** Overall length: 337 mm (Tip: 20 mm)

Tip diameter: 4.0 mm (Body: 12 mm)

Distance from probe tip to dipole centers: 1.5 mm



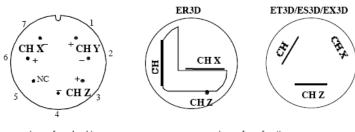
Figure 4-1 E-field Free-space Probe

#### **Probe Tip Description**

HAC field measurements take place in the close near field with high gradients. Increasing the measuring distance from the source will generally decrease the measured field values (in case of the validation dipole approx. 10% per mm).

The electric field probes have an irregular internal geometry because it is physically not possible to have the 3 orthogonal sensors situated with the same center. The effect of the different sensor centers is accounted for in the HAC uncertainty budget ("sensor displacement").

#### Connector Plan



(seen from back) (seen from front)

The antistatic shielding inside the probe is connected to the probe connector case.

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#### **Instrumentation Chain**

#### **Equation 1**

#### Conversion of Connector Voltage u, to E-Field E,

$$E_i = \sqrt{\frac{u_i + (u_i^2 \cdot CF)/(DCP)}{Norm_i \cdot ConvF}}$$

signal crest factor (peak power/average power)

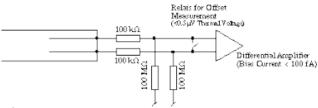
whereby

Eı: electric field in V/m

voltage of channel i at the connector in µV Uí. sensitivity of channel i in µV/(V/m)2 Norm: ConvF: enhancement factor in liquid (ConvF=1 for Air) DCP: diode compression point in µV

### Conditions of Calibration

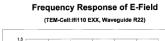
CF.



- a lower input impedance of the amplifier will result in different sensitivity factors Norm; and DCP
- larger bias currents will cause higher offset

## **Probe Response to Frequency**

The E-field sensors have inherently a very flat frequency response. They are calibrated with a number of frequencies resulting in a common calibration factor, with the frequency behavior documented in the calibration certificate (See also below).



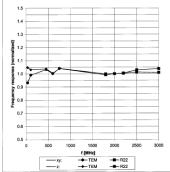


Figure 4-2 E-Field Probe Frequency Response

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#### **SPEAG Robotic System**

E-field measurements are performed using the DASY5 automated dosimetric assessment system. The DASY5 is made by Schmid & Partner Engineering AG (SPEAG) in Zurich, Switzerland and consists of high precision robotics system (Staubli), robot controller, Intel CORE i7 computer, near-field probe, probe alignment sensor, and the HAC phantom. The robot is a six-axis industrial robot performing precise movements to position the probe to the location (points) of maximum electromagnetic field (EMF).



Figure 4-3 SPEAG Robotic System

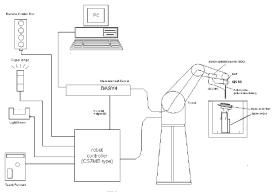
#### **System Hardware**

A cell controller system contains the power supply, robot controller, teach pendant (Joystick), and a remote control used to drive the robot motors. The PC consists of the computer with operating system and RF Measurement Software DASY5 v52.8 (with HAC Extension), A/D interface card, monitor, mouse, and keyboard. The Staubli Robot is connected to the cell controller to allow software manipulation of the robot. A data acquisition electronic (DAE) circuit that performs the signal amplification, signal multiplexing, AD-conversion, offset measurements, mechanical surface detection, collision detection, etc. is connected to the Electro-optical coupler (EOC). The EOC performs the conversion from the optical into digital electric signal of the DAE and transfers data to the PC plug-in card.

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#### **System Electronics**

The DAE consists of a highly sensitive electrometer-grade preamplifier with auto-zeroing, a channel and gain-switching multiplexer, a fast 16 bit AD-converter and a command decoder and control logic unit. Transmission to the PC-card is accomplished through an optical downlink for data and status information and an optical uplink for commands and clock lines. The mechanical probe mounting device includes two different sensor systems for frontal and sidewise probe contacts. They are also used for mechanical surface detection and probe collision detection. The robot uses its own controller with a built in VME-bus computer.



**Figure 4-4**SPEAG Robotic System Diagram

#### **DASY5 Instrumentation Chain**

The first step of the evaluation is a linearization of the filtered input signal to account for the compression characteristics of the detector diode. The compensation depends on the input signal, the diode type and the DC-transmission factor from the diode to the evaluation electronics. If the exciting field is pulsed, the crest factor of the signal must be known to correctly compensate for peak power. The formula for each channel can be given as:

$$\begin{aligned} V_i &= U_i + U_i^2 \cdot \frac{cf}{dcp_i} \\ \text{with} \quad V_i &= \text{compensated signal of channel i} & (i = x, y, z) \\ U_i &= \text{input signal of channel i} & (i = x, y, z) \\ cf &= \text{crest factor of exciting field} & (\text{DASY parameter}) \\ dcp_i &= \text{diode compression point} & (\text{DASY parameter}) \end{aligned}$$

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From the compensated input signals the primary field data for each channel can be evaluated:

E – field  
probes : 
$$E_i = \sqrt{\frac{V_i}{Norm_i \cdot ConvF}}$$

with  $V_i$  = compensated signal of channel i  $Norm_i$  = sensor sensitivity of channel i (i = x, y, z)(i = x, v, z)

 $\mu V/(V/m)^2$  for E-field Probes

= sensitivity enhancement in solution

= electric field strength of channel i in V/m

The RSS value of the field components gives the total field strength (Hermitian magnitude):

$$E_{tot} = \sqrt{E_x^2 + E_y^2 + E_z^2}$$

The primary field data are used to calculate the derived field units.

The measurement/integration time per point, as specified by the system manufacturer is >500ms.

The signal response time is evaluated as the time required by the system to reach 90% of the expected final value after an on/off switch of the power source with an integration time of 500ms and a probe response time of <5 ms. In the current implementation, DASY5 waits longer than 100ms after having reached the grid point before starting a measurement, i.e., the response time uncertainty is negligible.

If the device under test does not emit a CW signal, the integration time applied to measure the electric field at a specific point may introduce additional uncertainties due to the discretization. The tolerances for the different systems had the worst-case of 2.6%.

#### **Environmental Conditions**

Environmental conditions such as temperature and relative humidity are monitored to ensure there are no impacts on system specifications. Proper voltage and power line frequency conditions are maintained with three phase power sources. Environmental noise and reflections are monitored through system checks.

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#### TEST PROCEDURE 5.

#### **RF EMISSIONS**

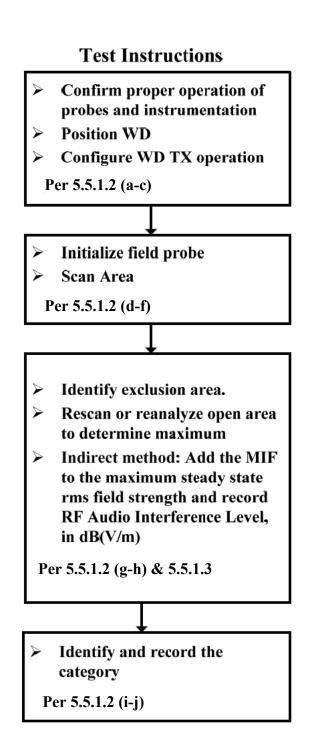


Figure 5-1 RF Emissions Flow Chart

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## **Test Setup**

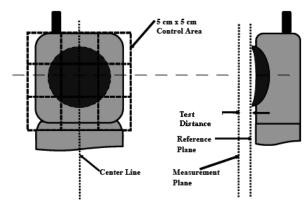


Figure 5-2 E-Field Emissions Test Setup Diagram (See Test Photographs for actual WD scan grid overlay)

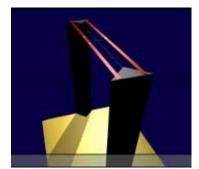


Figure 5-3 **HAC** Phantom

#### **RF Emissions Test Procedure:**

The following illustrate a typical RF emissions test scan over a wireless communications device:

- 1. Proper operation of the field probe, probe measurement system, other instrumentation, and the positioning system was confirmed.
- 2. WD is positioned in its intended test position, acoustic output point of the device perpendicular to the field probe.
- 3. The WD operation for maximum rated RF output power was configured and confirmed with the base station simulator, at the test channel and other normal operating parameters as intended for the test. The battery was ensured to be fully charged before each test.
- 4. The center sub-grid was centered over the center of the acoustic output (also audio band magnetic output, if applicable). The WD audio output was positioned tangent (as physically possible) to the measurement plane.
- 5. A surface calibration was performed before each setup change to ensure repeatable spacing and proper maintenance of the measurement plane using the HAC Phantom.
- 6. The measurement system measured the field strength at the reference location.
- 7. Measurements at 2mm or 5mm increments in the 5 x 5 cm region were performed at a distance 15 mm from the center point of the probe measurement element to the WD. A 360° rotation about the azimuth axis at the maximum interpolated position was measured. For the worst-case condition, the peak reading from this rotation was used in re-evaluating the HAC category.
- 8. The system performed a drift evaluation by measuring the field at the reference location. If the power drift deviated by more than 5%, the HAC test and drift measurements were repeated.

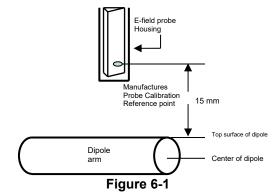
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#### 6. SYSTEM CHECK

#### I. System Check Parameters

The input signal was an un-modulated continuous wave. The following points were taken into consideration in performing this check:

- Average Input Power P = 100mW RMS (20dBm RMS) after adjustment for return loss
- The test fixture must meet the 2 wavelength separation criterion
- The proper measurement of the 15 mm probe to dipole separation, which is measured from top surface of the dipole to the calibration reference point of the sensor, defined by the probe manufacturer is shown in the following diagram:



Separation Distance from Dipole to Field Probe

RF power was recorded using both an average reading meter and a peak reading meter. Readings of the probe are provided by the measurement system.

To assure proper operation of the near-field measurement probe the input power to the dipole shall be commensurate with the full rated output power of the wireless device [e.g. - for a cellular phone wireless device the average peak antenna input power will be on the order of 100mW (20dBm) RMS] after adjustment for any mismatch.

#### II. Validation Procedure

A dipole antenna meeting the requirements given in C63.19 was placed in the position normally occupied by the WD.

The length of the dipole was scanned, and the average peak value was recorded.

#### **Measurement of CW**

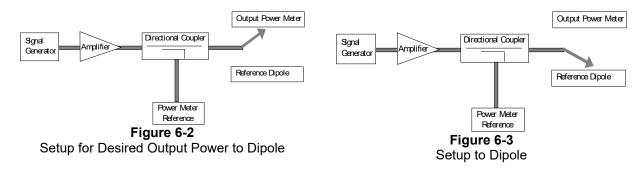
Using the near-field measurement system, scan the antenna over the radiating dipole and record the greatest field reading observed. Due to the nature of E-fields about free-space dipoles, the two E-field peaks measured over the dipole are averaged to compensate for non-parallelity of the setup (see manufacturer method on dipole calibration certificates, page 2). Field strength measurements shall be made only when the probe is stationary.

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RF power was recorded using both an average and a peak power reading meter.



Using this setup configuration, the signal generator was adjusted for the desired output power (100mW) at a specified frequency. The reference power from the coupled port of the directional coupler is recorded. Next, the output cable is connected to the reference dipole, as shown in Figure 6-3.

The input signal level was adjusted until the reference power from the coupled port of the directional coupler was the same as previously recorded, to compensate for the impedance mismatch between the output cable and the reference dipole. To assure proper operation of the near-field measurement probe the input power to the reference dipole was verified to the full rated output power of the wireless device. The dipole was secured in a holder in a manner to meet the 20 dB reflection. The near-field measurement probe was positioned over the dipole. The antenna was scanned over the appropriate sized area to cover the dipole from end to end. SPEAG uses 2D interpolation algorithms between the measured points. Please see below two dimensional plots showing that the interpolated values interpolate smoothly between 5mm steps for a free-space RF dipole:



2-D Raw Data from scan along dipole axis

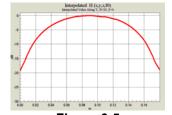
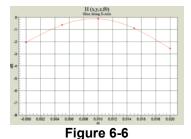


Figure 6-5
2-D Interpolated points from scan along dipole axis



2-D Raw Data from scan along transverse axis



2-D Interpolated points from scan along transverse axis

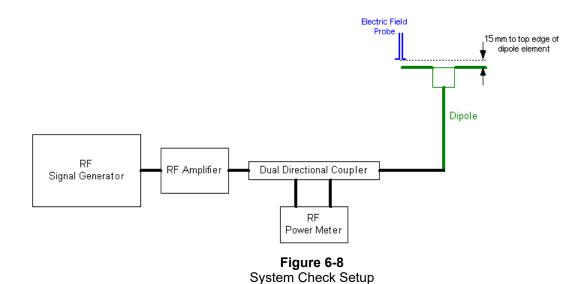
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# **III. System Check Results**

#### **Validation Results**

Date	Frequency (MHz)	Probe S/N	DAE S/N	Dipole S/N	Input Power (dBm)	E-field Result (V/m)	Target Field (V/m)	% Deviation
	835	4035	1415	1003	20.0	106.3	105.2	1.0%
4/29/2019	1880	4035	1415	1137	20.0	89.7	87.8	2.2%
	2600	4035	1415	1012	20.0	85.1	85.2	-0.1%



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#### 7. **MODULATION INTERFERENCE FACTOR**

### I. Measuring Modulation Interference Factors

For any specific fixed and repeatable modulated signal, a modulation interference factor (MIF, expressed in dB) may be determined that relates its interference potential to its steady-state RMS signal level or average power level. This factor is a function only of the audio-frequency amplitude modulation characteristics of the signal and is the same for field-strength and conducted power measurements. The MIF is valid only for a specific repeatable audio-frequency amplitude modulation characteristic; any change in modulation characteristic requires determination and application of a new MIF.

The MIF may be determined using a radiated RF field or a conducted RF signal:

- a. Using RF illumination or conducted coupling, apply the specific modulated signal in question to the measurement system at a level within its confirmed operating dynamic range.
- b. Measure the steady-state RMS level at the output of the fast probe or sensor.
- Measure the steady-state average level at the weighting output.
- Without changing the square-law detector or weighting system, and using RF illumination or conducted coupling, substitute for the specific modulated signal a 1 kHz, 80% amplitude modulated carrier at the same frequency and adjust its strength until the level at the weighting output equals the step c) measurement.
- e. Without changing the carrier level from step d), remove the 1 kHz modulation and again measure the steady-state RMS level indicated at the output of the fast probe or sensor.
- The MIF for the specific modulation characteristic is provided by the ratio of the step e) measurement to the step b) measurement, expressed in dB (20 × log[(step e)/(step b)]).

The following procedure was used to measure the MIF using the SPEAG Audio Interference Analyzer (AIA), Type No: SE UMS 170 CB, Serial No.: 1010:

- 1. The device was placed into a simulated call using a base station simulator or set to transmit using test software for a given mode.
- 2. The device was then set to continuously transmit at maximum power.
- 3. Using a coupler if needed, the device output signal was connected to the RF In port of the AIA, which was connected to a desktop computer. Alternatively, a radiated RF signal may be used with the AIA's built-in antenna.
- 4. The MIF measurement procedure in the DASY software was run, and the resulting MIF value was recorded.
- Steps 1-4 were repeated for all CMRS air interfaces, frequency bands, and modulations.

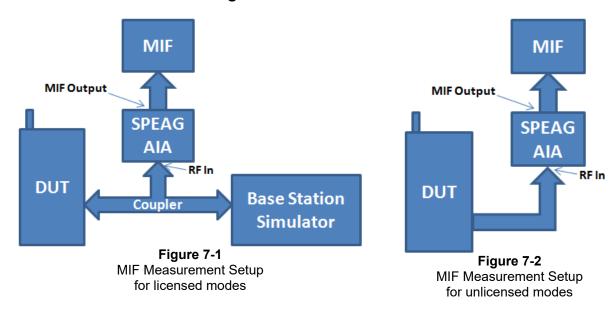
The modulation interference factors obtained were applied to readings taken of the actual wireless device in order to obtain an accurate audio interference level reading using the formula:

#### Audio Interference Level [dB(V/m)] = 20 \* log[Raw Field Value (V/m)] + MIF (dB)

Because the MIF value is output power independent, MIF values for a given mode should be constant across all devices; however, per C63.19-2011 §D.7, MIF values should be measured for each device being evaluated. The voice modes for this device have been investigated in this section of the report.

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## **II. MIF Measurement Block Diagrams**



### **III. Measured Modulation Interference Factors:**

Table 7-1 CDMA Modulation Interference Factors<sup>1</sup>

			C	ell	PCS			
Mode		908	22H	22H	22H	24E	24E	24E
		564	1013	384	777	25	600	1175
	RC1/SO3	2.93	2.90	2.89	2.95	2.85	2.81	2.99
CDMA	RC1/SO55	-17.31	-14.85	-14.90	-14.70	-15.01	-14.97	-18.97
	EvDO	-17.06	-14.58	-15.06	-15.14	-14.87	-15.12	-15.17

Table 7-2 GSM Modulation Interference Factors<sup>1</sup>

Mode			GSM850			GSM1900	
		128	190	251	512	661	810
GSM	Voice	3.52	3.52	3.52	3.50	3.50	3.50
GSW	EDGE	3.65	3.68	3.68	4.03	4.03	4.02

Table 7-3 UMTS Modulation Interference Factors<sup>1</sup>

OWI S Modulation interference ractors							13			
Mode			UMTS V			UMTS IV			UMTS II	
		4132	4183	4233	1312	1412	1513	9262	9400	9538
	12.2 kbps RMC	-20.82	-20.14	-18.70	-21.08	-21.19	-20.58	-21.73	-21.16	-21.28
UMTS	12.2 kbps AMR	-21.50	-21.07	-19.26	-21.70	-21.68	-21.58	-22.34	-21.85	-22.18
	HSUPA Subtest1	-19.83	-20.39	-19.50	-20.11	-20.65	-20.59	-20.36	-20.99	-21.24

<sup>&</sup>lt;sup>1</sup> Note: Measured MIF values may be lower than sample MIF values provided in ANSI C63.19-2011 Annex D.7 Table D.5 due to manufacturing variations for each device, however per Annex D.7, the sample MIF values of Table D.5 are not intended to substitute for measurements of actual devices under test and their respective operating modes.

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Table 7-4 LTE FDD Modulation Interference Factors<sup>1,2,3</sup>

	ETET DD Woddiation interference ractors											
LTE Band	Frequency [MHz]	Channel	Bandwidth [MHz]	Modulation	RB Size	RB Offset	MIF [dB]					
71	680.5	133297	20	16QAM	1	0	-9.66					
12	707.5	23095	10	16QAM	1	0	-9.78					
13	782.0	23230	10	16QAM	1	0	-9.80					
14	793.0	23330	10	16QAM	1	0	-9.86					
26	831.5	26865	15	16QAM	1	0	-9.67					
66	1745.0	132322	20	16QAM	1	0	-9.73					
25	1882.5	26365	20	16QAM	1	0	-10.26					
30	2310.0	27710	10	16QAM	1	0	-10.38					
7	2535.0	21100	20	16QAM	1	0	-10.15					
71	680.5	133297	20	QPSK	1	0	-14.77					
71	680.5	133297	20	64QAM	1	0	-9.51					
71	680.5	133297	20	64QAM	1	50	-9.55					
71	680.5	133297	20	64QAM	1	99	-9.43					
71	680.5	133297	20	64QAM	50	0	-16.53					
71	680.5	133297	20	64QAM	100	0	-16.84					
71	680.5	133297	15	64QAM	1	74	-9.86					
71	680.5	133297	10	64QAM	1	49	-9.62					
71	680.5	133297	5	64QAM	1	24	-9.97					

Table 7-5 LTE TDD B41 Power Class 3 Modulation Interference Factors<sup>1,4</sup>

LTE Band	Frequency [MHz]	Channel	Bandwidth [MHz]	Modulation	RB Size	RB Offset	MIF [dB]
41	2593.0	40620	20	16QAM	1	0	3.68
41	2593.0	40620	20	QPSK	1	0	3.63
41	2593.0	40620	20	64QAM	1	0	3.67
41	2593.0	40620	20	16QAM	1	50	3.67
41	2593.0	40620	20	16QAM	1	99	3.61
41	2593.0	40620	20	16QAM	50	0	3.60
41	2593.0	40620	20	16QAM	100	0	3.60
41	2593.0	40620	15	16QAM	1	0	3.68
41	2593.0	40620	10	16QAM	1	0	3.69
41	2593.0	40620	5	16QAM	1	0	3.62
41	2506.0	39750	10	16QAM	1	0	3.64
41	2549.5	40185	10	16QAM	1	0	3.61
41	2636.5	41055	10	16QAM	1	0	3.67
41	2680.0	41490	10	16QAM	1	0	3.65

Table 7-6 LTE TDD B41 Power Class 2 Modulation Interference Factors<sup>1,4</sup>

LTE Band	Frequency [MHz]	Channel	Bandwidth [MHz]	Modulation	RB Size	RB Offset	MIF [dB]
41	2593.0	40620	20	16QAM	1	0	3.72
41	2593.0	40620	20	QPSK	1	0	3.71
41	2593.0	40620	20	64QAM	1	0	3.75
41	2593.0	40620	20	64QAM	1	50	3.62
41	2593.0	40620	20	64QAM	1	99	3.69
41	2593.0	40620	20	64QAM	50	0	3.62
41	2593.0	40620	20	64QAM	100	0	3.63
41	2593.0	40620	15	64QAM	1	0	3.65
41	2593.0	40620	10	64QAM	1	0	3.68
41	2593.0	40620	5	64QAM	1	0	3.74
41	2506.0	39750	20	64QAM	1	0	3.72
41	2549.5	40185	20	64QAM	1	0	3.65
41	2636.5	41055	20	64QAM	1	0	3.71
41	2680.0	41490	20	64QAM	1	0	3.79

<sup>&</sup>lt;sup>1</sup> Note: Measured MIF values may be lower than sample MIF values provided in ANSI C63.19-2011 Annex D.7 Table D.5 due to manufacturing variations for each device, however per Annex D.7, the sample MIF values of Table D.5 are not intended to substitute for measurements of actual devices under test and their respective operating modes.

<sup>&</sup>lt;sup>4</sup> Note: LTE TDD MIFs were taken using UL-DL Configuration 5. More information about the chosen UL-DL Configuration can be found in Section 10.

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<sup>&</sup>lt;sup>2</sup> Note: All FDD LTE bands were found to have substantially similar MIF values given similar RB, BW, and modulation configurations.

<sup>&</sup>lt;sup>3</sup> Note: Since LTE Band 71 at 20 MHz bandwidth is the overall worst-case LTE MIF and does not support 3 nonoverlapping channels, MIF measurements were made only on the middle channel.

#### Table 7-7

802.11b (2.4GHz, SISO) Modulation Interference Factors<sup>1,2</sup>

	802.11b MIF Measurements [dB]								
Mode	Data Rate [Mbps]								
	1	2	5.5	11					
802.11b	-14.36	-10.75	-10.14	-10.36					

#### Table 7-8

802.11g (2.4GHz, SISO) Modulation Interference Factors<sup>1,2</sup>

002.1	602: 119 (2: 16112, 6166) Meddiation interference i detere											
		802.11g MIF Measurements [dB]										
Mode		Data Rate [Mbps]										
	6	9	12	18	24	36	48	54				
802.11g	-8.07	-6.92	-6.11	-5.27								

#### Table 7-9

802.11n (2.4GHz, SISO) Modulation Interference Factors<sup>1,2</sup>

		802.11n (2.4GHz) MIF Measurements [dB]								
Mode		Data Rate [Mbps]								
	6.5	13	19.5	26	39	52	58.5	65		
802.11n	-8.10	-6.23	-5.25	-4.84	-4.37	-4.18	-4.23	-4.35		

#### **Table 7-10**

802.11a (5GHz, 20MHz BW, SISO) Modulation Interference Factors<sup>1,2</sup>

•		802.11a MIF Measurements [dB]									
Mode		Data Rate [Mbps]									
	6	9	12	18	24	36	48	54			
802.11a	-8.31	-7.04	-6.18	-5.33	-4.61	-4.21	-4.10	-4.32			

#### **Table 7-11**

802.11n (5GHz, 20MHz BW, SISO) Modulation Interference Factors<sup>1,2</sup>

		20MHz BW 802.11n (5GHz) MIF Measurements [dB]									
Mode		Data Rate [Mbps]									
	6.5	13	19.5	26	39	52	58.5	65			
802.11n	-8.24	-6.31	-5.29	-4.88	-4.43	-4.24	-4.33	-4.40			

#### **Table 7-12**

802.11ac (5GHz, 20MHz BW, SISO) Modulation Interference Factors<sup>1,2</sup>

	ì	20MHz BW 802.11ac (5GHz) MIF Measurements [dB]									
Mode		Data Rate [Mbps]									
	6.5	13	19.5	26	39	52	58.5	65	78		
802.11ac	-8.44	-6.33	-5.27	-4.88	-4.39	-4.23	-4.28	-4.36	-4.50		

#### **Table 7-13**

802.11n (5GHz, 40MHz BW, SISO) Modulation Interference Factors<sup>1,2</sup>

		40MHz BW 802.11n (5GHz) MIF Measurements [dB]									
Mode		Data Rate [Mbps]									
	13.5	27	40.5	54	81	108	121.5	135			
802.11n	-6.02	-4.67	-4.25	-4.33	-4.52	-4.93	-5.06	-5.00			

<sup>&</sup>lt;sup>1</sup> Note: Measured MIF values may be lower than sample MIF values provided in ANSI C63.19-2011 Annex D.7 Table D.5 due to manufacturing variations for each device, however per Annex D.7, the sample MIF values of Table D.5 are not intended to substitute for measurements of actual devices under test and their respective operating modes.

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<sup>&</sup>lt;sup>2</sup> Note: WIFI MIF values were found to be independent of the transmit channel.

#### **Table 7-14**

802.11ac (5GHz, 40MHz BW, SISO) Modulation Interference Factors<sup>1,2</sup>

	40MHz BW 802.11ac (5GHz) MIF Measurements [dB]									
Mode		Data Rate [Mbps]								
	13.5	27	40.5	54	81	108	121.5	135	180	
802.11ac	-6.02	-4.63	-4.23	-4.30	-4.50	-4.89	-5.01	-4.93	-5.34	

#### **Table 7-15**

802.11ac (5GHz, 80MHz BW, SISO) Modulation Interference Factors<sup>1,2</sup>

00-		· · · · - ,   ·		,	,	/ medalation interiored ractors					
	80MHz BW 802.11ac (5GHz) MIF Measurements [dB]										
Mode		Data Rate [Mbps]  29.3   58.5   87.8   117   175.5   234   263.3   292.5   351   390									
	29.3										
802.11ac	-4.51	-4.21	-4.59	-4.92	-5.39	-5.72	-5.85	-5.72	-6.14	-5.98	

<sup>1</sup> Note: Measured MIF values may be lower than sample MIF values provided in ANSI C63.19-2011 Annex D.7 Table D.5 due to manufacturing variations for each device, however per Annex D.7, the sample MIF values of Table D.5 are not intended to substitute for measurements of actual devices under test and their respective operating modes.

<sup>2</sup> Note: WIFI MIF values were found to be independent of the transmit channel.

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#### 8. RF CONDUCTED POWER MEASUREMENTS

# I. Procedures Used to Establish RF Signal for HAC Testing

The handset was placed into a simulated call using a base station simulator in a shielded chamber. Such test signals offer a consistent means for testing HAC and are recommended for evaluating HAC. Measurements were taken with a fully charged battery. In order to verify that the device was tested and maintained at full power, this was configured with the base station simulator.

#### II. HAC Measurement Conditions

#### **Output Power Verification**

Maximum output power is verified on the High, Middle and Low channels for all applicable air interfaces. See Table 8-1 for air interface specific settings of transmit power parameters.

> Table 8-1 **Power Control Parameters and Settings by Air Interface**

Air Interface:	Parameter Name:	Parameter Set To:		
CDMA	Power Control Bits	"All Up"		
GSM	PCL	GSM850: "5"; GSM1900: "0"		
UMTS	TPC	"All 1's"		
LTE	TPC	"Max Power"		
WIFI	PLS	Mfr Specified		

## III. Setup Used to Measure RF Conducted Powers

Power measurements for licensed modes were performed using a base station simulator under digital average power. Power measurements for unlicensed modes were performed using a power meter and power sensor.

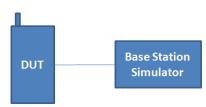


Figure 8-1 Power Measurement Setup for licensed modes

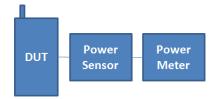


Figure 8-2 Power Measurement Setup for unlicensed modes

#### IV. CDMA Conducted Powers

Band	Channel	Rule Part	Frequency	SO2 [dBm]	SO2 [dBm]	SO2 [dBm]	SO55 [dBm]	SO55 [dBm]	SO75 [dBm]	SO9 [dBm]	SO9 [dBm]	SO3 [dBm]	SO3 [dBm]	SO3 [dBm]	1x EvDO Rev. A [dBm]
	F-RC		MHz	RC1	RC3	RC4	RC1	RC3	RC11	RC2	RC5	RC1	RC3	RC4	(RETAP)
Cellular	564	90S	820.1	24.21	24.26	24.19	24.26	24.19	23.90	24.22	24.16	24.06	24.20	24.20	24.34
	1013	22H	824.7	24.29	24.23	24.25	24.32	24.18	24.04	24.34	24.22	24.14	24.22	24.26	24.54
Cellular	384	22H	836.52	24.21	24.12	24.13	24.23	24.03	23.93	24.23	24.13	24.12	24.12	24.14	24.43
	777	22H	848.31	23.86	23.85	23.70	23.70	23.92	23.96	23.59	23.74	23.67	23.89	23.82	24.05
	25	24E	1851.25	24.68	24.66	24.62	24.67	24.62	24.48	24.66	24.67	24.48	24.65	24.65	24.52
PCS	600	24E	1880	24.68	24.69	24.63	24.68	24.65	24.75	24.68	24.68	24.54	24.68	24.67	24.33
	1175	24E	1908.75	24.58	24.59	24.53	24.57	24.53	24.80	24.57	24.58	24.54	24.59	24.57	24.21

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# **V. GSM Conducted Powers**

Band	Channel	GSM [dBm] CS (1 Slot)	EDGE [dBm] 1 Tx Slot	
	128	32.39	26.29	
GSM 850	190	32.61	26.53	
	251	32.65	26.70	
	512	29.86	25.88	
GSM 1900	661	29.42	25.42	
	810	29.28	25.60	

## **VI. UMTS Conducted Powers**

Mode	3GPP 34.121	Cellular Band [dBm]			AWS Band [dBm]			PCS Band [dBm]		
Subtest		4132	4183	4233	1312	1412	1513	9262	9400	9538
WCDMA	12.2 kbps RMC	24.98	25.00	25.00	24.15	24.15	24.53	23.88	24.21	24.38
WCDIVIA	12.2 kbps AMR	25.00	24.96	25.00	24.17	24.13	24.48	23.88	24.23	24.37
HSUPA	Subtest 1	19.68	19.69	19.71	18.95	18.83	19.16	19.38	19.52	19.85

#### VII. **LTE Conducted Powers**

# a. LTE Band 71

Table 8-2 LTE Band 71 (680.5MHz) Conducted Powers - 20MHz Bandwidth

	,		Mid Channel		
Modulation	RB Size	RB Offset	133297 (680.5 MHz)	MPR Allowed per 3GPP [dB]	MPR [dB]
			Conducted Power [dBm]	JOI 1 [ub]	
	1	0	24.21		0
	1	50	24.05	0	0
	1	99	23.88		0
QPSK	50	0	22.98		1
	50	25	22.88	0-1	1
	50	50	22.81	0-1	1
	100	0	22.85		1
	1	0	22.96		1
	1	50	22.80	0-1	1
	1	99	22.66		1
16QAM	50	0	22.02		2
	50	25	21.91	0-2	2
	50	50	21.81	0-2	2
	100	0	21.92		2
	1	0	22.08		2
	1	50	21.96	0-2	2
	1	99	21.70		2
64QAM	50	0	20.89		3
	50	25	20.78	0-3	3
	50	50	20.76	0-3	3
	100	0	20.84		3

Note: Since LTE Band 71 at 20MHz bandwidth does not support 3 non-overlapping channels, conducted power measurements were made only on the middle channel.

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Table 8-3 LTE Band 71 (680.5MHz) Conducted Powers – 15MHz Bandwidth

	(	0.0111112	O O I I G G G G G G G G G G G G G G G G		z Banawiath
Modulation	RB Size	RB Offset	Mid Channel 133297 (680.5 MHz) Conducted Power [dBm]	MPR Allowed per 3GPP [dB]	MPR [dB]
	1	0	23.83		0
	1	36	23.78	0	0
	1	74	23.70		0
QPSK	36	0	22.89		1
	36	18	22.89	0-1	1
	36	37	22.81	0-1	1
	75	0	22.85		1
	1	0	22.73		1
	1	36	22.70	0-1	1
	1	74	22.75		1
16QAM	36	0	21.90		2
	36	18	21.84	0-2	2
	36	37	21.82	0-2	2
	75	0	21.90		2
	1	0	21.87		2
	1	36	21.90	0-2	2
	1	74	21.79		2
64QAM	36	0	20.90		3
	36	18	20.86	0-3	3
	36	37	20.84	] 0-3	3
	75	0	20.82		3

Note: Since LTE Band 71 at 15MHz bandwidth does not support 3 non-overlapping channels, conducted power measurements were made only on the middle channel.

> Table 8-4 LTE Band 71 (680.5MHz) Conducted Powers – 10MHz Bandwidth

ETE Band TT (000.0MHz) Conducted Towers - Town 12 Bandwidth										
Modulation	RB Size	RB Offset	Low Channel 133172 (668.0 MHz)	Mid Channel 133297 (680.5 MHz)	High Channel 133422 (693.0 MHz)	MPR Allowed per 3GPP [dB]	MPR [dB]			
			C	Conducted Power [dBm	]					
	1	0	23.56	23.85	23.88		0			
	1	25	23.92	23.80	23.77	0	0			
	1	49	23.92	23.75	23.76		0			
QPSK	25	0	23.05	22.87	22.90		1			
	25	12	23.01	22.88	22.88	0-1	1			
	25	25	22.97	22.84	22.86	U- I	1			
	50	0	22.99	22.83	22.88		1			
	1	0	22.80	22.77	22.85	0-1	1			
	1	25	22.89	22.70	22.78		1			
	1	49	22.75	22.67	22.78		1			
16QAM	25	0	22.11	21.95	21.93		2			
	25	12	22.07	21.92	21.92	0-2	2			
	25	25	22.03	21.93	21.89	0-2	2			
	50	0	22.02	21.88	21.94		2			
	1	0	22.19	21.90	21.96		2			
	1	25	22.15	21.96	21.94	0-2	2			
	1	49	22.01	21.91	21.91		2			
64QAM	25	0	20.94	20.89	20.90		3			
	25	12	20.93	20.86	20.87	0-3	3			
	25	25	20.94	20.85	20.87	0-3	3			
	50	0	20.96	20.83	20.88		3			

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Table 8-5 LTE Band 71 (680.5MHz) Conducted Powers - 5MHz Bandwidth

LTE Ballu / 1 (600.5MHz) Collaucted Fowers - 5MHz Balluwidth							
			Low Channel	Mid Channel	High Channel		
Modulation RB Size	RB Offset	133147 (665.5 MHz)	133297 (680.5 MHz)	133447 (695.5 MHz)	MPR Allowed per 3GPP [dB]	MPR [dB]	
			(	Conducted Power [dBm	]		
	1	0	23.98	23.80	23.80		0
	1	12	24.00	23.81	23.77	0	0
	1	24	23.95	23.81	23.72		0
QPSK	12	0	23.03	22.88	22.83		1
	12	6	23.04	22.87	22.83	0-1	1
	12	13	23.03	22.87	22.89		1
	25	0	22.99	22.89	22.81		1
	1	0	22.91	22.85	22.75	0-1	1
	1	12	22.93	22.77	22.79		1
	1	24	22.90	22.83	22.80		1
16QAM	12	0	22.05	21.93	21.93		2
	12	6	22.03	21.92	21.92	0-2	2
	12	13	21.97	21.90	21.90	0-2	2
	25	0	21.98	21.94	21.89		2
	1	0	21.90	21.83	21.90		2
	1	12	21.93	21.83	21.85	0-2	2
	1	24	21.85	21.74	21.92		2
64QAM	12	0	20.89	20.80	20.82		3
	12	6	20.88	20.76	20.79	0.3	3
	12	13	20.87	20.75	20.78	0-3	3
	25	0	20.94	20.81	20.77		3

# b. LTE Band 12

Table 8-6 LTE Band 12 (707.5MHz) Conducted Powers - 10MHz Bandwidth

ETE Bana TE (TOTTOMTE)			<b></b>	L Banamatn	
Modulation	RB Size	RB Offset	Mid Channel 23095 (707.5 MHz)  Conducted Power [dBm]	MPR Allowed per 3GPP [dB]	MPR [dB]
	1	0	24.55		0
	1	25	24.45	0	0
	1	49	24.30		0
QPSK	25	0	23.38		1
	25	12	23.33	0.4	1
	25	25	23.27	0-1	1
	50	0	23.35		1
	1	0	23.33		1
	1	25	23.28	0-1	1
	1	49	23.15		1
16QAM	25	0	22.39		2
	25	12	22.34	0-2	2
	25	25	22.29	0-2	2
	50	0	22.36		2
	1	0	22.29		2
	1	25	22.21	0-2	2
	1	49	22.03		2
64QAM	25	0	21.28		3
	25	12	21.25	0-3	3
	25	25	21.19	0-3	3
	50	0	21.24		3

Note: Since LTE Band 12 at 10MHz bandwidth does not support 3 non-overlapping channels, conducted power measurements were made only on the middle channel.

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Table 8-7 LTE Band 12 (707.5MHz) Conducted Powers – 5MHz Bandwidth

			Low Channel	nel Mid Channel High Channel			
Modulation RB Size		RB Offset	23035 (701.5 MHz)	23095 (707.5 MHz)	23155 (713.5 MHz)	MPR Allowed per 3GPP [dB]	MPR [dB]
	Conducted Power [dBm]				]		
	1	0	24.37	24.45	24.54		0
	1	12	24.32	24.37	24.55	0	0
	1	24	24.35	24.35	24.33		0
QPSK	12	0	23.32	23.36	23.50		1
	12	6	23.29	23.34	23.46	0-1	1
	12	13	23.28	23.35	23.47		1
	25	0	23.27	23.34	23.47		1
	1	0	23.34	23.27	23.40	0-1	1
	1	12	23.30	23.22	23.41		1
	1	24	23.25	23.23	23.29		1
16QAM	12	0	22.30	22.42	22.47		2
	12	6	22.29	22.42	22.46	0-2	2
	12	13	22.28	22.40	22.48	0-2	2
	25	0	22.31	22.40	22.46		2
	1	0	22.26	22.30	22.56		2
	1	12	22.31	22.16	22.48	0-2	2
	1	24	22.32	22.13	22.34		2
64QAM	12	0	21.23	21.23	21.33		3
	12	6	21.23	21.22	21.28	0-3	3
	12	13	21.23	21.19	21.34	0-3	3
	25	0	21.26	21.24	21.34		3

Table 8-8 LTE Band 12 (707.5MHz) Conducted Powers – 3MHz Bandwidth

LTE Band 12 (707.5WIHZ) Conducted Powers - SWIHZ Bandwidth							
			Low Channel	Mid Channel	High Channel		
Madulation	Modulation RB Size	DD Offeet	23025	23095	23165	MPR Allowed per	MDD (4D)
Wodulation	KD SIZE	RB Offset	(700.5 MHz)	(707.5 MHz)	(714.5 MHz)	3GPP [dB]	MPR [dB]
			C	Conducted Power [dBm	]		
	1	0	24.37	24.44	24.45		0
	1	7	24.38	24.42	24.50	0	0
	1	14	24.37	24.47	24.42		0
QPSK	8	0	23.34	23.41	23.45		1
	8	4	23.32	23.40	23.46	0-1	1
	8	7	23.32	23.38	23.42	U- I	1
	15	0	23.25	23.35	23.41		1
	1	0	23.23	23.30	23.25		1
	1	7	23.20	23.38	23.31	0-1	1
	1	14	23.28	23.35	23.41		1
16QAM	8	0	22.30	22.37	22.45		2
	8	4	22.31	22.44	22.44	0-2	2
	8	7	22.30	22.39	22.44	0-2	2
	15	0	22.29	22.35	22.45		2
	1	0	22.37	22.35	22.35		2
	1	7	22.34	22.37	22.36	0-2	2
	1	14	22.30	22.42	22.30		2
64QAM	8	0	21.13	21.28	21.24		3
	8	4	21.15	21.30	21.27	0-3	3
	8	7	21.14	21.28	21.26	0-3	3
15	0	21.24	21.29	21.32		3	

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Table 8-9 LTE Band 12 (707.5MHz) Conducted Powers – 1.4MHz Bandwidth

		I L Dania	12 (101.5141112)	Conducted PC	/WCI3 — 1. <del>-</del> 18111	z Danawiani	
			Low Channel	Mid Channel	High Channel		
Modulation	Modulation RB Size	RB Offset	23017 (699.7 MHz)	23095 (707.5 MHz)	23173 (715.3 MHz)	MPR Allowed per 3GPP [dB]	MPR [dB]
			(	Conducted Power [dBm	]		
	1	0	24.31	24.35	24.44		0
	1	2	24.25	24.31	24.41		0
	1	5	24.27	24.32	24.00		0
QPSK	3	0	24.25	24.36	24.37	0	0
	3	2	24.26	24.37	24.35		0
	3	3	24.25	24.38	24.36	0-1	0
	6	0	23.27	23.36	23.40		1
	1	0	23.21	23.21	23.20	0-1	1
	1	2	23.15	23.27	23.25		1
	1	5	23.22	23.20	23.30		1
16QAM	3	0	23.39	23.39	23.41		1
	3	2	23.36	23.34	23.47		1
	3	3	23.35	23.35	23.43		1
	6	0	22.35	22.34	22.45	0-2	2
	1	0	22.39	22.42	22.38		2
	1	2	22.42	22.45	22.43		2
	1	5	22.43	22.34	22.51	0-2	2
64QAM	3	0	22.20	22.32	22.37	0-2	2
	3	2	22.19	22.35	22.41		2
	3	3	22.18	22.28	22.44		2
	6	0	21.28	21.30	21.33	0-3	3

# c. LTE Band 13

**Table 8-10** LTE Band 13 (780.0MHz) Conducted Powers – 10MHz Bandwidth

			Mid Channel		
Modulation	RB Size	RB Offset	23230 (782.0 MHz)	MPR Allowed per 3GPP [dB]	MPR [dB]
			Conducted Power [dBm]	JOI 1 [ub]	
	1	0	24.63		0
	1	25	24.60	0	0
	1	49	24.53		0
QPSK	25	0	23.47		1
	25	12	23.41	0-1	1
	25	25	23.37	0-1	1
	50	0	23.39		1
	1	0	23.42		1
	1	25	23.38	0-1	1
	1	49	23.27		1
16QAM	25	0	22.44		2
	25	12	22.40	0-2	2
	25	25	22.34	0-2	2
	50	0	22.41		2
	1	0	22.49		2
	1	25	22.39	0-2	2
	1	49	22.29		2
64QAM	25	0	21.34		3
	25	12	21.33	0-3	3
	25	25	21.28	0-3	3
	50	0	21.34		3

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**Table 8-11** LTE Band 13 (780.0MHz) Conducted Powers - 5MHz Bandwidth

				1	
			Mid Channel		
Modulation	RB Size	RB Offset	23230	MPR Allowed per	MPR [dB]
Modulation	IND OILC	ND Olloct	(782.0 MHz)	3GPP [dB]	iiii it [ub]
			Conducted Power		
	4	0	[dBm]		0
	1	0	24.52	1	0
	1	12	24.53	0	0
	1	24	24.51		0
QPSK	12	0	23.50		1
	12	6	23.50	0-1	1
	12	13	23.40	0-1	1
	25	0	23.50		1
	1	0	23.41		1
	1	12	23.45	0-1	1
	1	24	23.44	1	1
16QAM	12	0	22.54		2
	12	6	22.52	0-2	2
	12	13	22.51	0-2	2
	25	0	22.45		2
	1	0	22.30		2
	1	12	22.30	0-2	2
	1	24	22.29	1	2
64QAM	12	0	21.43		3
	12	6	21.40	1	3
	12	13	21.36	0-3	3
	25	0	21.41	1	3

Note: Since LTE Band 13 at 5MHz bandwidth does not support 3 non-overlapping channels, conducted power measurements were made only on the middle channel.

#### d. LTE Band 14

**Table 8-12** LTE Band 14 (793.0MHz) Conducted Powers – 10MHz Bandwidth

LIL Dallu 14 (733.0191112			Conducted F	OWEIS - IUIVII	iz Bandwidth
Modulation	RB Size	RB Offset	Mid Channel 23330 (793.0 MHz)  Conducted Power [dBm]	MPR Allowed per 3GPP [dB]	MPR [dB]
	1	0	24.48		0
	1	25	24.40	0	0
	1	49	24.26		0
QPSK	25	0	23.28		1
	25	12	23.26	0-1	1
	25	25	23.19	0-1	1
	50	0	23.26	1	1
	1	0	23.43		1
	1	25	23.29	0-1	1
	1	49	23.19	1	1
16QAM	25	0	22.30		2
	25	12	22.23	0-2	2
	25	25	22.18	0-2	2
	50	0	22.25		2
	1	0	22.45		2
	1	25	22.37	0-2	2
	1	49	22.22		2
64QAM	25	0	21.19		3
	25	12	21.12	0-3	3
	25	25	21.08	0-3	3
	50	0	21.17		3

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**Table 8-13** LTE Band 14 (793.0MHz) Conducted Powers - 5MHz Bandwidth

		00.0.11.1 IL	- Conaactoa i		- Danawatii
			Mid Channel		
Modulation	RB Size	RB Offset	23330	MPR Allowed per	MPR [dB]
Woddiation		KB Oliset	(793.0 MHz)	3GPP [dB]	IIII IX [GD]
			Conducted Power		
			[dBm]		
	1	0	23.56		0
	1	12	23.53	0	0
	1	24	23.51		0
QPSK	12	0	22.51		1
	12	6	22.49	0-1	1
	12	13	22.48	0-1	1
	25	0	22.48		1
	1	0	22.21		1
	1	12	22.31	0-1	1
	1	24	22.29		1
16QAM	12	0	21.45		2
	12	6	21.46	0-2	2
	12	13	21.43	0-2	2
	25	0	21.50		2
	1	0	21.34		2
	1	12	21.38	0-2	2
	1	24	21.23	1	2
64QAM	12	0	20.44		3
	12	6	20.43		3
	12	13	20.40	0-3	3
	25	0	20.46	1	3

Note: Since LTE Band 14 at 5MHz bandwidth does not support 3 non-overlapping channels, conducted power measurements were made only on the middle channel.

#### e. LTE Band 26

**Table 8-14** LTE Band 26 (831.5MHz) Conducted Powers - 15MHz Bandwidth

		J 110111112)		OWOIC TOWNIE Banawiati		
Modulation	RB Size	RB Offset	Mid Channel 26865 (831.5 MHz) Conducted Power [dBm]	MPR Allowed per 3GPP [dB]	MPR [dB]	
	1	0	24.75		0	
	1	36	24.64	0	0	
	1	74	24.76		0	
QPSK	36	0	23.52		1	
	36	18	23.48	0.1	1	
	36	37	23.46	0-1	1	
	75	0	23.48		1	
	1	0	23.50		1	
	1	36	23.42	0-1	1	
	1	74	23.32		1	
16QAM	36	0	22.50		2	
	36	18	22.47	0-2	2	
	36	37	22.42	0-2	2	
	75	0	22.51		2	
	1	0	22.65		2	
	1	36	22.53	0-2	2	
	1	74	22.47		2	
64QAM	36	0	21.49		3	
	36	18	21.41	0-3	3	
	36	37	21.40	0-3	3	
	75	0	21.44		3	

Note: Since LTE Band 26 at 15MHz bandwidth does not support 3 non-overlapping channels, conducted power measurements were made only on the middle channel.

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**Table 8-15** LTE Band 26 (831.5MHz) Conducted Powers - 10MHz Bandwidth

LTE Ballu 20 (031.5MHz) Colludcted Powers - Tollinz Balluwidth									
			Low Channel	Mid Channel	High Channel				
Modulation	RB Size	RB Offset	26740	26865	26990	MPR Allowed per	MPR [dB]		
Wodulation	KD Size	KB Oliset	(819.0 MHz)	(831.5 MHz)	(844.0 MHz)	3GPP [dB]	WIFK [UD]		
			(	Conducted Power [dBm	]				
	1	0	24.75	24.85	24.98		0		
	1	25	24.69	24.82	24.92	0	0		
	1	49	24.67	24.76	24.80		0		
QPSK	25	0	23.66	23.68	23.82		1		
	25	12	23.65	23.67	23.79	0-1	1		
	25	25	23.64	23.65	23.77		1		
	50	0	23.65	23.67	23.78		1		
	1	0	23.62	23.80	23.81	0-1	1		
	1	25	23.67	23.73	23.80		1		
	1	49	23.59	23.69	23.15		1		
16QAM	25	0	22.65	22.67	22.86		2		
	25	12	22.63	22.63	22.82	0-2	2		
	25	25	22.62	22.64	22.83	0-2	2		
	50	0	22.56	22.65	22.83		2		
	1	0	22.64	22.62	22.82		2		
	1	25	22.66	22.55	22.81	0-2	2		
	1	49	22.62	22.49	22.25		2		
64QAM	25	0	21.60	21.67	21.78	0-3	3		
	25	12	21.60	21.65	21.75		3		
	25	25	21.60	21.63	21.77		3		
	50	0	21.58	21.62	21.75		3		

**Table 8-16** LTE Band 26 (831.5MHz) Conducted Powers - 5MHz Bandwidth

		LIL Dail	1 26 (63 1.5WITZ	<i>j</i> odriaucteu i	OWEIS - GIVII IZ	Danawiatii	
			Low Channel	Mid Channel	High Channel		
Modulation	RB Size	RB Offset	26715	26865	27015	MPR Allowed per	MPR [dB]
Wodulation	KD Size	KB Oliset	(816.5 MHz)	(831.5 MHz)	(846.5 MHz)	3GPP [dB]	INIPK [UD]
			Conducted Power [dBm]				
	1	0	24.70	24.75	24.82		0
	1	12	24.69	24.73	24.84	0	0
	1	24	24.67	24.73	24.77		0
QPSK	12	0	23.69	23.70	23.83		1
	12	6	23.67	23.68	23.84	0-1	1
	12	13	23.68	23.70	23.84		1
	25	0	23.69	23.67	23.80		1
	1	0	23.65	23.57	23.75	0-1	1
	1	12	23.70	23.57	23.76		1
	1	24	23.54	23.43	23.72		1
16QAM	12	0	22.64	22.66	22.86		2
	12	6	22.65	22.66	22.84	0-2	2
	12	13	22.64	22.67	22.85	0-2	2
	25	0	22.58	22.61	22.83		2
	1	0	22.62	22.56	22.79		2
	1	12	22.57	22.54	22.73	0-2	2
	1	24	22.52	22.49	22.77		2
64QAM	12	0	21.60	21.55	21.79	0-3	3
	12	6	21.60	21.54	21.78		3
	12	13	21.55	21.57	21.77		3
	25	0	21.59	21.64	21.76		3

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**Table 8-17** LTE Band 26 (831.5MHz) Conducted Powers – 3MHz Bandwidth

LTE Band 20 (00 1.0Mill2) Conducted 1 Owers - SMill2 Bandwidth								
			Low Channel	Mid Channel	High Channel			
Modulation	RB Size	RB Offset	26705	26865	27025	MPR Allowed per	MPR [dB]	
Modulation	IND GIZE	TID OHOU	(815.5 MHz)	(831.5 MHz)	(847.5 MHz)	3GPP [dB]	iii it [ab]	
			(	Conducted Power [dBm	]			
	1	0	24.70	24.72	24.87		0	
	1	7	24.69	24.69	24.88	0	0	
	1	14	24.65	24.73	24.91		0	
QPSK	8	0	23.67	23.74	23.87		1	
	8	4	23.71	23.70	23.88	0-1	1	
	8	7	23.71	23.69	23.90		1	
	15	0	23.64	23.65	23.84		1	
	1	0	23.62	23.63	23.75	0-1	1	
	1	7	23.45	23.62	23.83		1	
	1	14	23.68	23.54	23.80		11	
16QAM	8	0	22.67	22.65	22.89		2	
	8	4	22.62	22.64	22.91	0-2	2	
	8	7	22.63	22.68	22.89	0-2	2	
	15	0	22.58	22.64	22.85		2	
	1	0	22.65	22.61	22.73		2	
	1	7	22.70	22.62	22.72	0-2	2	
	1	14	22.69	22.65	22.73		2	
64QAM	8	0	21.54	21.57	21.76	0-3	3	
	8	4	21.53	21.56	21.77		3	
	8	7	21.55	21.60	21.79		3	
	15	0	21.61	21.68	21.82		3	

**Table 8-18** LTE Band 26 (831.5MHz) Conducted Powers – 1.4MHz Bandwidth

LTE Band 26 (831.5MHz) Conducted Powers – 1.4MHz Bandwidth									
Modulation	RB Size	RB Offset	Low Channel 26697 (814.7 MHz)	Mid Channel 26865 (831.5 MHz)	High Channel 27033 (848.3 MHz)	MPR Allowed per 3GPP [dB]	MPR [dB]		
				Conducted Power [dBm					
	1	0	24.67	24.63	24.89		0		
	1	2	24.72	24.59	24.86		0		
	1	5	24.68	24.72	24.88	0	0		
QPSK	3	0	24.63	24.60	24.77	U	0		
	3	2	24.62	24.59	24.78		0		
	3	3	24.63	24.60	24.85		0		
	6	0	23.70	23.65	23.86	0-1	1		
	1	0	23.77	23.50	23.69	0-1	1		
	1	2	23.80	23.49	23.65		1		
	1	5	23.79	23.53	23.69		1		
16QAM	3	0	23.75	23.70	23.86	0-1	1		
	3	2	23.79	23.74	23.94		1		
	3	3	23.71	23.63	24.02		1		
	6	0	22.75	22.72	22.92	0-2	2		
	1	0	22.63	22.79	22.93		2		
	1	2	22.65	22.78	22.92		2		
	1	5	22.67	22.76	22.93	0-2	2		
64QAM	3	0	22.62	22.65	22.96	U-Z	2		
	3	2	22.65	22.67	22.94		2		
	3	3	22.62	22.65	22.93		2		
	6	0	21.66	21.56	21.74	0-3	3		

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## f. LTE Band 66

**Table 8-19** LTE Band 66 (1745.0MHz) Conducted Powers - 20MHz Bandwidth

			Low Channel	Mid Channel	High Channel		
Modulation	RB Size	RB Offset	132072 (1720.0 MHz)	132322 (1745.0 MHz)	132572 (1770.0 MHz)	MPR Allowed per 3GPP [dB]	MPR [dB]
			(	Conducted Power [dBm	]		
	1	0	24.05	24.07	24.24		0
	1	50	23.95	23.84	24.07	0	0
	1	99	23.70	23.61	23.93		0
QPSK	50	0	22.88	22.77	22.91		1
	50	25	22.81	22.67	22.81	0-1	1
	50	50	22.74	22.60	22.72		1
ĺ	100	0	22.80	22.65	22.83		1
	1	0	22.88	22.66	23.01	0-1	1
	1	50	22.74	22.45	22.86		1
	1	99	22.58	22.22	22.73		1
16QAM	50	0	21.88	21.80	21.87		2
	50	25	21.78	21.67	21.82	0-2	2
	50	50	21.75	21.57	21.74	0-2	2
	100	0	21.80	21.71	21.80		2
	1	0	21.95	22.03	22.01		2
	1	50	21.79	21.77	21.81	0-2	2
	1	99	21.59	21.61	21.64		2
64QAM	50	0	20.90	20.82	20.83	0-3	3
	50	25	20.85	20.72	20.71		3
	50	50	20.79	20.59	20.66		3
	100	0	20.92	20.73	20.79		3

**Table 8-20** LTE Band 66 (1745.0MHz) Conducted Powers - 15MHz Bandwidth

ETE Band 60 (17461611112) Conducted 1 GWO16 TOWN 12 Bandwidth								
			Low Channel	Mid Channel	High Channel			
Modulation	RB Size	RB Offset	132047	132322	132597	MPR Allowed per	MPR [dB]	
Wiodulation	KD SIZE	KB Oliset	(1717.5 MHz)	(1745.0 MHz)	(1772.5 MHz)	3GPP [dB]	WIFK [UD]	
				Conducted Power [dBm	]			
	1	0	24.14	24.11	24.23		0	
	1	36	24.00	23.96	24.13	0	0	
	1	74	23.90	23.76	24.06		0	
QPSK	36	0	23.03	22.98	23.09		1	
	36	18	22.98	22.89	23.03	0-1	1	
	36	37	22.89	22.82	22.98	0-1	1	
	75	0	22.95	22.90	23.03		1	
	1	0	23.00	23.21	23.15	0-1	1	
	1	36	22.85	22.93	23.09		1	
	1	74	22.87	22.87	22.93		1	
16QAM	36	0	22.14	21.97	22.08		2	
	36	18	22.01	21.89	22.05	0-2	2	
	36	37	21.95	21.82	22.00	0-2	2	
	75	0	22.02	21.91	22.03		2	
	1	0	22.17	22.09	22.00		2	
	1	36	22.04	21.90	21.92	0-2	2	
	1	74	21.95	21.78	21.76		2	
64QAM	36	0	21.04	20.94	20.98	0-3	3	
	36	18	21.01	20.85	20.93		3	
	36	37	20.96	20.75	20.89		3	
	75	0	20.97	20.89	20.90		3	

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**Table 8-21** LTE Band 66 (1745.0MHz) Conducted Powers – 10MHz Bandwidth

LIL Dand 00 (1745.0MHz) Conducted Fowers - 10MHz Dandwidth									
			Low Channel	Mid Channel	High Channel				
Modulation	RB Size	RB Offset	132022	132322	132622	MPR Allowed per	MPR [dB]		
Modulation	IND OIZE	ND Oliset	(1715.0 MHz)	(1745.0 MHz)	(1775.0 MHz)	3GPP [dB]	Will IX [GD]		
			(	Conducted Power [dBm	1]				
	1	0	24.06	24.07	24.20		0		
	1	25	23.95	23.95	24.13	0	0		
	1	49	23.88	23.90	24.08		0		
QPSK	25	0	22.90	22.93	23.02		1		
	25	12	22.86	22.87	23.03	0-1	1		
	25	25	22.83	22.80	22.99		1		
	50	0	22.87	22.86	23.00		1		
	1	0	23.00	22.86	23.30	0-1	1		
	1	25	22.87	22.72	23.15		1		
	1	49	22.80	22.61	22.95		1		
16QAM	25	0	22.03	21.98	22.11		2		
	25	12	21.94	21.96	22.08	0-2	2		
	25	25	21.92	21.90	22.04	0-2	2		
	50	0	21.93	21.91	22.02		2		
	1	0	21.79	21.93	22.00		2		
	1	25	21.78	21.83	21.98	0-2	2		
	1	49	21.72	21.71	21.94		2		
64QAM	25	0	20.98	21.01	20.98	0-3	3		
	25	12	20.97	20.94	20.94		3		
	25	25	20.88	20.86	20.90		3		
	50	0	20.89	20.91	20.92		3		

**Table 8-22** LTE Band 66 (1745 0MHz) Conducted Powers - 5MHz Bandwidth

LTE Band 66 (1745.0MHz) Conducted Powers – 5MHz Bandwidth									
			Low Channel	Mid Channel	High Channel				
Modulation	RB Size	RB Offset	131997 (1712.5 MHz)	132322 (1745.0 MHz)	132647 (1777.5 MHz)	MPR Allowed per 3GPP [dB]	MPR [dB]		
	Conducted Power [dBm]								
	1	0	23.82	24.00	24.15		0		
	1	12	23.80	23.90	24.12	0	0		
	1	24	23.84	23.85	24.13		0		
QPSK	12	0	0 22.86 22.90 23.07		1				
	12	6	22.82	22.86	23.04	0-1	1		
	12	13	22.79	22.85	23.03		1		
	25	0	22.82	22.86	23.04		1		
	1	0	22.77	22.73	23.05	0-1	1		
	1	12	22.74	22.61	23.03		1		
	1	24	22.82	22.60	22.90		1		
16QAM	12	0	21.93	21.95	22.06		2		
	12	6	21.90	21.90	22.02	0-2	2		
	12	13	21.88	21.85	22.03		2		
	25	0	21.87	21.91	22.00		2		
	1	0	21.86	21.80	22.05		2		
	1	12	21.89	21.70	22.02	0-2	2		
	1	24	21.84	21.83	21.94		2		
64QAM	12	0	20.86	20.90	20.92		3		
	12	6	20.84	20.85	20.91	0-3	3		
	12	13	20.82	20.80	20.92		3		
	25	0	20.81	20.83	20.94		3		

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**Table 8-23** LTE Band 66 (1745.0MHz) Conducted Powers - 3MHz Bandwidth

ETE Band 00 (1740.0Min2) Conducted Towers - SMin2 Bandwidth								
			Low Channel	Mid Channel	High Channel			
Modulation	RB Size	RB Offset	131987	132322	132657	MPR Allowed per	MPR [dB]	
Wodulation	KD Size	KB Oliset	(1711.5 MHz)	(1745.0 MHz)	(1778.5 MHz)	3GPP [dB]	WIFK [UD]	
			(	Conducted Power [dBm	1]			
	1	0	23.88	24.03	24.07		0	
	1	7	23.87	23.95	24.05	0	0	
	1	14	23.86	23.92	24.06		0	
QPSK	8	0	22.85	22.89	23.02		1	
	8	4	22.84	22.90	23.02	0-1	1	
	8	7	22.81	22.89	23.03		1	
	15	0	22.80	22.82	22.98		1	
	1	0	22.90	22.93	22.86	0-1	1	
	1	7	22.93	22.78	22.84		1	
	1	14	22.73	22.84	22.85		1	
16QAM	8	0	21.85	21.95	22.02		2	
	8	4	21.84	21.93	22.01	0-2	2	
	8	7	21.82	21.86	21.98	0-2	2	
	15	0	21.83	21.87	21.99		2	
	1	0	21.83	21.76	21.89		2	
	1	7	21.80	21.77	22.02	0-2	2	
	1	14	21.79	21.74	21.98		2	
64QAM	8	0	20.84	20.80	20.92	0-3	3	
	8	4	20.86	20.78	20.89		3	
	8	7	20.82	20.77	20.91		3	
	15	0	20.90	20.89	20.91		3	

**Table 8-24** LTE Band 66 (1745.0MHz) Conducted Powers - 1.4MHz Bandwidth

LTE Dana 00 (1745.0MHz) Conducted 1 Owers - 1.4MHz Danawidth										
			Low Channel	Mid Channel	High Channel					
Modulation	RB Size	RB Offset	131979 (1710.7 MHz)	132322 (1745.0 MHz)	132665 (1779.3 MHz)	MPR Allowed per 3GPP [dB]	MPR [dB]			
			(	Conducted Power [dBm	]					
	1	0	23.82	23.89	23.98		0			
	1	1 2 23.83 23.87 23.97	23.97		0					
	1	5	23.86	23.89	24.01	0	0			
QPSK	3	0	23.78	23.85	23.96		0			
	3	2	23.80	23.82	23.96		0			
	3	3	23.78	23.82	23.93		0			
	6	0	22.84	22.83	22.97	0-1	1			
	1	0	22.78	22.66	22.83	0-1	1			
	1	2	22.69	22.62	22.92		1			
	1	5	22.77	22.75	22.94		1			
16QAM	3	0	23.00	22.96	23.05		1			
	3	2	22.99	23.00	23.10		1			
	3	3	22.94	22.89	23.00		1			
	6	0	21.94	21.90	21.89	0-2	2			
	1	0	21.71	21.94	21.97		2			
	1	2	21.70	21.91	21.98		2			
	1	5	21.69	21.87	21.99	0-2	2			
64QAM	3	0	21.93	21.89	21.93	0-2	2			
	3	2	21.92	21.88	21.90		2			
	3	3	21.92	21.89	21.92		2			
	6	0	20.92	20.80	20.81	0-3	3			

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# g. LTE Band 25

**Table 8-25** LTE Band 25 (1882.5MHz) Conducted Powers - 20MHz Bandwidth

ETE Band 20 (1002:011112) Conducted 1 Owers 2011112 Bandwidth									
Modulation	RB Size	RB Offset	Low Channel 26140 (1860.0 MHz)	Mid Channel 26365 (1882.5 MHz) Conducted Power [dBm	High Channel 26590 (1905.0 MHz)	MPR Allowed per 3GPP [dB]	MPR [dB]		
	1	0	24.03	24.10	24.45		0		
	1	50	24.00	24.06	24.41	0	0		
	1	99	23.96	24.03	24.40		0		
QPSK	50	0	22.92	22.99	23.25		1		
	50	25	22.94	22.94	23.23	0.1	1		
	50	50	22.88	22.93	23.24	0-1	1		
	100	0	22.86	22.97	23.24		1		
	1	0	22.88	22.93	23.23	0-1	1		
	1	50	22.84	22.92	23.13		1		
	1	99	22.78	22.89	23.11		1		
16QAM	50	0	22.00	22.03	22.34		2		
	50	25	21.96	22.02	22.24	0-2	2		
	50	50	21.97	21.99	22.23	0-2	2		
	100	0	21.89	21.96	22.24		2		
	1	0	21.90	22.18	22.37		2		
	1	50	22.02	22.11	22.25	0-2	2		
	1	99	21.90	22.09	22.19		2		
64QAM	50	0	20.94	21.05	21.32	0-3	3		
	50	25	20.95	21.01	21.18		3		
	50	50	20.96	20.96	21.20		3		
i	100	0	20.93	21.04	21.31		3		

**Table 8-26** LTE Band 25 (1882.5MHz) Conducted Powers – 15MHz Bandwidth

ETE Dana 23 (1002.3Wit2) Conducted Towers - 13Wit2 Danawidth									
			Low Channel	Mid Channel	High Channel				
Modulation	RB Size	RB Offset	26115	26365	26615	MPR Allowed per	MPR [dB]		
	112 0.20	112 0001	(1857.5 MHz)	(1882.5 MHz)	(1907.5 MHz)	3GPP [dB]			
			(	Conducted Power [dBm	]				
	1	0	23.87	24.14	24.39		0		
	1	36	23.88	24.04	24.32	0	0		
	1	74	23.90	23.96	24.33		0		
QPSK	36	0	22.94	22.98	23.27		1		
	36	18	22.93	22.98	23.28	0-1	1		
	36	37	22.95	22.96	23.28	0-1	1		
	75	0	22.94	22.97	23.25		1		
	1	0	22.80	22.90	23.32	0-1	1		
	1	36	22.81	22.82	23.28		1		
	1	74	22.75	22.73	23.23		1		
16QAM	36	0	22.03	22.03	22.24		2		
	36	18	22.01	22.03	22.25	0-2	2		
	36	37	22.03	22.00	22.25	0-2	2		
	75	0	22.02	22.04	22.29		2		
	1	0	21.73	21.75	22.11		2		
	1	36	21.85	21.66	22.14	0-2	2		
	1	74	21.81	21.63	22.15		2		
64QAM	36	0	20.93	20.92	21.08	0-3	3		
	36	18	20.94	20.85	21.08		3		
	36	37	20.90	20.89	21.15		3		
	75	0	20.89	20.88	21.18		3		

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**Table 8-27** LTE Band 25 (1882.5MHz) Conducted Powers – 10MHz Bandwidth

ETE Bana 20 (100210111112) Gonadotod 1 ovroid 10111112 Banaviatin							
Modulation	RB Size	RB Offset	Low Channel 26090 (1855.0 MHz)	Mid Channel 26365 (1882.5 MHz) Conducted Power [dBm	High Channel 26640 (1910.0 MHz)	MPR Allowed per 3GPP [dB]	MPR [dB]
	1	0	23.91	24.00	24.25		0
	1	25	23.90	24.02	24.21	0	0
	1	49	23.93	23.99	24.18	_	0
QPSK	25	0	22.92	22.98	23.20		1
	25	12	22.94	22.95	23.22	2.4	1
	25	25	22.93	22.96	23.23	0-1	1
	50	0	22.93	22.96	23.25		1
	1	0	22.75	22.97	23.03	0-1	1
	1	25	22.76	22.95	23.06		1
	1	49	22.75	22.98	23.02		1
16QAM	25	0	22.02	22.02	22.27		2
	25	12	22.05	22.03	22.28	0-2	2
	25	25	22.05	22.03	22.29	0-2	2
	50	0	22.00	22.02	22.30		2
	1	0	21.77	21.79	22.02		2
	1	25	21.83	21.77	22.10	0-2	2
	1	49	21.87	21.72	22.09		2
64QAM	25	0	20.92	20.90	21.17	0-3	3
	25	12	20.93	20.89	21.18		3
	25	25	20.94	20.92	21.17		3
	50	0	20.88	20.90	21.15		3

**Table 8-28** LTE Band 25 (1882.5MHz) Conducted Powers - 5MHz Bandwidth

	LTE Band 25 (1882.5MHz) Conducted Fowers – 5MHz Bandwidth										
			Low Channel	Mid Channel	High Channel						
Modulation	RB Size	RB Offset	26065	26365	26665	MPR Allowed per	MPR [dB]				
Wiodulation	KD SIZE	RB Oliset	(1852.5 MHz)	(1882.5 MHz)	(1912.5 MHz)	3GPP [dB]	WIFK [UD]				
			(	Conducted Power [dBm	]						
	1	0	23.97	24.03	24.31		0				
	1	12	23.98	23.98	24.29	0	0				
	1	24	23.99	23.99	24.31		0				
QPSK	12	0	22.96	22.99	23.30		1				
	12	6	22.98	22.97	23.30	0-1	1				
	12	13	22.96	22.96	23.30		1				
	25	0	22.97	22.97	23.32		1				
	1	0	22.62	22.75	22.92	0-1	1				
	1	12	22.68	22.72	22.89		1				
	1	24	22.67	22.73	22.91		1				
16QAM	12	0	22.10	22.04	22.36		2				
	12	6	22.08	22.03	22.39	0-2	2				
	12	13	22.12	22.01	22.38	0-2	2				
	25	0	22.04	22.05	22.39		2				
	1	0	21.95	21.67	22.22		2				
	1	12	21.97	21.59	22.28	0-2	2				
	1	24	22.00	21.69	22.23		2				
64QAM	12	0	20.96	20.81	21.21	0-3	3				
	12	6	20.92	20.81	21.19		3				
	12	13	20.95	20.82	21.20		3				
	25	0	20.92	20.85	21.20		3				

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**Table 8-29** LTE Band 25 (1882.5MHz) Conducted Powers – 3MHz Bandwidth

ETE Band 25 (1002.0Mill2) Conducted I Owers - SMill2 Bandwidth								
Modulation	RB Size	RB Offset	Low Channel 26055 (1851.5 MHz)	Mid Channel 26365 (1882.5 MHz)	High Channel 26675 (1913.5 MHz)	MPR Allowed per 3GPP [dB]	MPR [dB]	
				Conducted Power [dBm	]			
	1	0	23.94	24.00	24.31		0	
	1	7	23.95	23.96	24.30	0	0	
	1	14	23.93	23.99	24.35		0	
QPSK	8	0	22.97	22.93	23.29		1	
	8	4	22.96	22.97	23.30	0-1	1	
	8	7	23.00	22.96	23.30	0-1	1	
	15	0	22.99	22.96	23.32		1	
	1	0	22.87	22.92	23.25	0-1	1	
	1	7	23.00	22.92	23.10		1	
	1	14	23.01	22.89	23.03		1	
16QAM	8	0	22.00	22.00	22.38		2	
	8	4	22.02	21.97	22.40	0-2	2	
	8	7	22.02	21.98	22.37	0-2	2	
	15	0	21.98	22.02	22.13		2	
	1	0	21.92	21.70	22.21		2	
	1	7	21.92	21.80	22.15	0-2	2	
	1	14	21.95	21.79	22.10		2	
64QAM	8	0	20.83	20.86	21.20	0-3	3	
	8	4	20.84	20.91	21.21		3	
	8	7	20.85	20.85	21.19		3	
1	15	0	20.94	20.82	21.24		3	

**Table 8-30** LTE Band 25 (1882.5MHz) Conducted Powers - 1.4MHz Bandwidth

	Lie Band 25 (1662.5MHz) Conducted Powers - 1.4MHz Bandwidth								
Modulation	RB Size	RB Offset	Low Channel 26047 (1850.7 MHz)	Mid Channel 26365 (1882.5 MHz)	High Channel 26683 (1914.3 MHz)	MPR Allowed per 3GPP [dB]	MPR [dB]		
			(	Conducted Power [dBm	]				
	1	0	23.85	23.92	24.22		0		
	1	2	23.84	23.89	24.21		0		
	1	5	23.88	23.94	24.25	0	0		
QPSK	3	0	23.88	23.90	24.21		0		
	3	2	23.89	23.90	24.24	0-1	0		
	3	3	23.90	23.89	24.22		0		
	6	0	23.00	22.96	23.30		1		
	1	0	22.92	22.75	23.36	0-1	1		
	1	2	22.90	22.73	23.35		1		
	1	5	22.88	22.80	23.34		1		
16QAM	3	0	22.94	22.91	23.37		1		
	3	2	22.96	22.87	23.36		1		
	3	3	22.92	22.91	23.31		1		
	6	0	22.07	21.97	22.34	0-2	2		
	1	0	21.97	21.85	22.23		2		
	1	2	21.97	21.96	22.27		2		
	1	5	22.00	22.00	22.20	0-2	2		
64QAM	3	0	21.94	21.84	22.24	0-2	2		
	3	2	21.98	21.83	22.27		2		
	3	3	21.97	21.82	22.25		2		
	6	0	20.99	20.74	21.10	0-3	3		

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## h. LTE Band 30

**Table 8-31** LTE Band 30 (2310.0MHz) Conducted Powers - 10MHz Bandwidth

	(=-		, conducted i	• • • • • • • • • • • • • • • • • • • •	<u> </u>
Modulation	RB Size	RB Offset	Mid Channel 27710 (2310.0 MHz) Conducted Power [dBm]	MPR Allowed per - 3GPP [dB]	MPR [dB]
	1	0	24.57		0
	1	25	24.55	0	0
	1	49	23.97		0
QPSK	25	0	23.19		1
	25	12	23.17	0-1	1
	25	25	23.17	0-1	1
	50	0	23.13		1
	1	0	22.98		1
	1	25	22.87	0-1	1
	1	49	22.86		1
16QAM	25	0	22.10		2
	25	12	22.14	0-2	2
	25	25	22.13	0-2	2
	50	0	22.08		2
	1	0	21.91		2
	1	25	22.18	0-2	2
	1	49	22.05		2
64QAM	25	0	21.19		3
	25	12	21.20	0-3	3
	25	25	21.14	0-3	3
	50	0	21.17		3

**Table 8-32** LTE Band 30 (2310.0MHz) Conducted Powers - 5MHz Bandwidth

	1110 30 (Z	J 10.01411 12	.) Conducted i	Owers - Sivinz	Danawiani
Modulation	RB Size	RB Offset	Mid Channel 27710 (2310.0 MHz) Conducted Power [dBm]	MPR Allowed per 3GPP [dB]	MPR [dB]
	1	0	24.56		0
	1	12	24.62	0	0
	1	24	24.61		0
QPSK	12	0	23.57		1
	12	6	23.61	0-1	1
	12	13	23.60	0-1	1
	25	0	23.61		1
	1	0	23.45		1
	1	12	23.44	0-1	1
	1	24	23.42		1
16QAM	12	0	22.35		2
	12	6	22.35	0-2	2
	12	13	22.42	0-2	2
	25	0	22.40		2
	1	0	22.34		2
	1	12	22.44	0-2	2
	1	24	22.34		2
64QAM	12	0	21.31		3
	12	6	21.35	0-3	3
	12	13	21.37	J-5	3
	25	0	21.39		3

Note: Since LTE Band 30 at 5MHz bandwidth does not support 3 non-overlapping channels, conducted power measurements were made only on the middle channel.

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## i. LTE Band 7

**Table 8-33** LTE Band 7 (2535.0MHz) Conducted Powers - 20MHz Bandwidth

	ETE Bana / (2000:0111112) Conducted I Owers - Zollinz Banawiath						
Modulation	RB Size	RB Offset	Low Channel 20850 (2510.0 MHz)	Mid Channel 21100 (2535.0 MHz) Conducted Power [dBm	High Channel 21350 (2560.0 MHz)	MPR Allowed per 3GPP [dB]	MPR [dB]
	1	0	23.32	23.27	23.51		0
	1	50	23.22	23.30	23.47	0	0
	1	99	23.15	23.40	23.37		0
QPSK	50	0	22.12	22.14	22.32		1
	50	25	22.08	22.16	22.30	0.4	1
	50	50	22.04	22.19	22.26	0-1	1
	100	0	22.10	22.15	22.28		1
	1	0	22.17	22.17	22.45	0-1	1
	1	50	22.11	22.20	22.34		1
	1	99	22.06	22.30	22.24		1
16QAM	50	0	21.10	21.18	21.38		2
	50	25	21.08	21.19	21.34	0-2	2
	50	50	21.06	21.25	21.29	0-2	2
	100	0	21.08	21.18	21.31		2
	1	0	21.14	21.17	21.45		2
	1	50	21.06	21.22	21.37	0-2	2
	1	99	21.01	21.28	21.28		2
64QAM	50	0	20.21	20.25	20.49	0-3	3
	50	25	20.16	20.28	20.44		3
	50	50	20.15	20.33	20.40		3
	100	0	20.24	20.34	20.52		3

**Table 8-34** LTE Band 7 (2535.0MHz) Conducted Powers - 15MHz Bandwidth

			Low Channel	Mid Channel	High Channel		
Madulatian	DD 0:	DD 0#4	20825	21100	21375	MPR Allowed per	MDD (-ID)
Modulation	RB Size	RB Offset	(2507.5 MHz)	(2535.0 MHz)	(2562.5 MHz)	3GPP [dB]	MPR [dB]
			(	Conducted Power [dBm	]		
	1	0	23.38	23.39	23.36		0
	1	36	23.36	23.39	23.33	0	0
	1	74	23.33	23.34	23.40		0
QPSK	36	0	22.33	22.31	22.33		1
	36	18	22.29	22.30	22.31	0-1	1
	36	37	22.30	22.31	22.30		1
	75	0	22.31	22.29	22.34		1
	1	0	22.50	22.33	22.20	0-1	1
	1	36	22.36	22.34	22.19		1
	1	74	22.36	22.36	22.17		1
16QAM	36	0	21.34	21.34	21.33		2
	36	18	21.34	21.34	21.33	0-2	2
	36	37	21.33	21.32	21.34	0-2	2
	75	0	21.35	21.33	21.35		2
	1	0	21.13	21.11	21.41		2
	1	36	21.15	21.17	21.35	0-2	2
	1	74	21.24	21.20	21.37		2
64QAM	36	0	20.28	20.19	20.31	0-3	3
	36	18	20.31	20.20	20.35		3
	36	37	20.28	20.21	20.34		3
	75	0	20.26	20.17	20.33		3

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**Table 8-35** LTE Band 7 (2535.0MHz) Conducted Powers - 10MHz Bandwidth

LIL Band / (2000.000112) Conducted Fowers - Town 12 Bandwidth							
			Low Channel	Mid Channel	High Channel		
Modulation	RB Size	RB Offset	20800	21100	21400	MPR Allowed per	MDD (4D)
Wodulation	RD Size	KB Oliset	(2505.0 MHz)	(2535.0 MHz)	(2565.0 MHz)	3GPP [dB]	MPR [dB]
				Conducted Power [dBm	]		
	1	0	23.42	23.40	23.39		0
	1	25	23.40	23.39	23.32	0	0
	1	49	23.41	23.40	23.41		0
QPSK	25	0	22.27	22.24	22.22		1
	25	12	22.28	22.25	22.21	0-1	1
	25	25	22.31	22.23	22.21		1
	50	0	22.30	22.22	22.25		1
	1	0	22.29	22.30	22.37	0-1	1
	1	25	22.30	22.20	22.40		1
	1	49	22.19	22.20	22.25		1
16QAM	25	0	21.37	21.33	21.34		2
	25	12	21.40	21.32	21.31	0-2	2
	25	25	21.42	21.29	21.30	0-2	2
	50	0	21.38	21.30	21.28		2
	1	0	21.16	21.10	21.15		2
	1	25	21.25	21.15	21.18	0-2	2
	1	49	21.25	21.17	21.20		2
64QAM	25	0	20.23	20.22	20.22	0-3	3
	25	12	20.25	20.23	20.27		3
	25	25	20.28	20.22	20.23		3
	50	0	20.22	20.21	20.24		3

**Table 8-36** LTE Band 7 (2535.0MHz) Conducted Powers - 5MHz Bandwidth

			Low Channel	Mid Channel	High Channel		
Modulation	RB Size	RB Offset	20775	21100	21425	MPR Allowed per	MPR [dB]
Modulation	IND OIL	IND CHOCK	(2502.5 MHz)	(2535.0 MHz)	(2567.5 MHz)	3GPP [dB]	iiii it [uD]
			C	Conducted Power [dBm	]		
	1	0	23.42	23.30	23.28		0
	1	12	23.41	23.29	23.29	0	0
	1	24	23.44	23.31	23.31		0
QPSK	12	0	22.34	22.28	22.23		1
	12	6	22.32	22.25	22.22	0-1	1
	12	13	22.31	22.24	22.23		1
	25	0	22.30	22.26	22.24		1
	1	0	22.28	22.27	22.09	0-1	1
	1	12	22.40	22.10	22.10		1
	1	24	22.34	22.15	22.11		1
16QAM	12	0	21.39	21.36	21.34		2
	12	6	21.40	21.35	21.32	0-2	2
	12	13	21.38	21.34	21.35	0-2	2
	25	0	21.39	21.29	21.27		2
	1	0	21.24	21.01	21.01		2
	1	12	21.30	21.03	21.09	0-2	2
	1	24	21.26	20.99	21.02		2
64QAM	12	0	20.25	20.17	20.15	0-3	3
	12	6	20.25	20.14	20.17		3
	12	13	20.30	20.17	20.16		3
	25	0	20.25	20.21	20.21		3

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# j. LTE Band 41 - Power Class 3

**Table 8-37** LTE Band 41 (2593.0MHz) Conducted Powers – 20MHz Bandwidth

			Low Channel	Low-Mid Channel	Mid Channel	Mid-High Channel	High Channel		
Modulation	RB Size	RB Offset	39750 (2506.0 MHz)	40185 (2549.5 MHz)	40620 (2593.0 MHz)	41055 (2636.5 MHz)	41490 (2680.0 MHz)	MPR Allowed per 3GPP [dB]	MPR [dB]
				Co	nducted Power [dE	Bm]			
	1	0	23.28	23.38	23.29	23.03	23.26		0
	1	50	23.24	23.37	23.14	23.06	23.20	0	0
	1	99	23.19	23.28	23.10	23.10	23.17		0
QPSK	50	0	22.34	22.47	22.31	22.09	22.30		1
	50	25	22.36	22.54	22.26	22.16	22.28	0-1	1
	50	50	22.23	22.43	22.21	22.05	22.26	0-1	1
	100	0	22.32	22.44	22.28	22.03	22.29		1
	1	0	22.29	22.35	22.41	21.73	22.32		1
	1	50	22.38	22.14	21.98	21.85	22.26	0-1	1
	1	99	22.27	22.06	21.99	21.84	22.12		1
16QAM	50	0	21.43	21.49	21.21	21.05	21.36		2
	50	25	21.36	21.46	21.28	21.02	21.25	0-2	2
	50	50	21.29	21.48	21.11	20.96	21.21	0-2	2
	100	0	21.36	21.39	21.22	20.99	21.29		2
	1	0	20.91	20.91	20.89	20.52	20.98		2
	1	50	20.79	20.82	20.84	20.70	21.18	0-2	2
	1	99	21.07	21.03	20.91	20.63	21.01		2
64QAM	50	0	20.27	20.45	20.38	20.10	20.59		3
	50	25	20.32	20.50	20.37	20.15	20.53	0-3	3
	50	50	20.27	20.53	20.28	20.15	20.54	0-3	3
	100	0	20.32	20.46	20.34	20.18	20.58		3

**Table 8-38** LTE Band 41 (2593.0MHz) Conducted Powers - 15MHz Bandwidth

			Low Channel	Low-Mid Channel	Mid Channel	Mid-High Channel	High Channel		
Modulation	RB Size	RB Offset	39750 (2506.0 MHz)	40185 (2549.5 MHz)	40620 (2593.0 MHz)	41055 (2636.5 MHz)	41490 (2680.0 MHz)	MPR Allowed per 3GPP [dB]	MPR [dB]
				Co	nducted Power [dE	Sm]			
	1	0	23.63	23.48	23.27	23.40	23.29		0
	1	36	23.53	23.49	23.23	23.43	23.33	0	0
	1	74	23.53	23.55	23.07	23.41	23.25		0
QPSK	36	0	22.37	22.26	22.08	22.19	22.21		1
	36	18	22.33	22.31	22.08	22.23	22.20	0-1	1
	36	37	22.32	22.31	22.06	22.26	22.22	0-1	1
	75	0	22.34	22.34	22.09	22.26	22.23		1
	1	0	22.54	22.31	22.05	22.24	22.05		1
	1	36	22.55	22.28	22.06	22.23	22.03	0-1	1
	1	74	22.45	22.42	22.01	22.25	22.01		1
16QAM	36	0	21.55	21.37	21.20	21.26	21.30		2
	36	18	21.55	21.41	21.17	21.20	21.25	0-2	2
	36	37	21.43	21.43	21.14	21.28	21.24	0-2	2
	75	0	21.47	21.43	21.19	21.37	21.30		2
	1	0	21.10	21.13	20.89	20.90	20.89		2
	1	36	21.13	21.18	20.80	20.98	20.72	0-2	2
	1	74	21.01	21.19	20.86	21.06	20.84		2
64QAM	36	0	20.54	20.39	20.20	20.35	20.33		3
	36	18	20.49	20.47	20.10	20.38	20.29	0-3	3
	36	37	20.51	20.47	20.22	20.35	20.27		3
	75	0	20.53	20.47	20.19	20.41	20.32		3

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**Table 8-39** LTE Band 41 (2593.0MHz) Conducted Powers – 10MHz Bandwidth

			· · · · · · · · · · · · · · · · · · ·						
			Low Channel	Low-Mid Channel	Mid Channel	Mid-High Channel	High Channel		
Modulation	RB Size	RB Offset	39750 (2506.0 MHz)	40185 (2549.5 MHz)	40620 (2593.0 MHz)	41055 (2636.5 MHz)	41490 (2680.0 MHz)	MPR Allowed per 3GPP [dB]	MPR [dB]
				Co	nducted Power [dB	ßm]			
	1	0	23.70	23.60	23.35	23.43	22.71		0
	1	25	23.65	23.60	23.40	23.46	22.71	0	0
	1	49	23.66	23.62	23.14	23.53	22.72		0
QPSK	25	0	22.35	22.31	22.08	22.14	21.67		1
	25	12	22.35	22.35	22.08	22.21	21.67	0-1	1
	25	25	22.34	22.38	22.05	22.22	21.66	0-1	1
	50	0	22.35	22.36	22.05	22.23	21.65		1
	1	0	22.41	22.31	22.03	22.05	21.44		1
	1	25	22.33	22.37	22.00	22.07	21.48	0-1	1
	1	49	22.33	22.44	21.95	22.21	21.47		1
16QAM	25	0	21.51	21.36	21.12	21.22	20.71		2
	25	12	21.39	21.41	21.13	21.26	20.68	0-2	2
	25	25	21.37	21.40	21.01	21.27	20.68	0-2	2
	50	0	21.49	21.49	21.21	21.36	20.79		2
	1	0	21.12	21.15	20.97	20.98	20.40		2
	1	25	21.04	21.24	20.91	20.99	20.43	0-2	2
	1	49	21.01	21.25	20.88	21.03	20.39		2
64QAM	25	0	20.52	20.44	20.15	20.33	19.76		3
	25	12	20.52	20.46	20.12	20.37	19.75	0-3	3
	25	25	20.42	20.34	20.12	20.37	19.76	0-3	3
	50	0	20.47	20.46	20.18	20.35	19.76		3

**Table 8-40** LTE Band 41 (2593.0MHz) Conducted Powers - 5MHz Bandwidth

	LTE Balla 41 (2595.0MHz) Collaucted Powers - 5MHz Ballawidth										
			Low Channel	Low-Mid Channel	Mid Channel	Mid-High Channel	High Channel				
Modulation	RB Size	RB Offset	39750 (2506.0 MHz)	40185 (2549.5 MHz)	40620 (2593.0 MHz)	41055 (2636.5 MHz)	41490 (2680.0 MHz)	MPR Allowed per 3GPP [dB]	MPR [dB]		
				Co	nducted Power [dB	m]					
	1	0	23.59	23.51	23.33	23.43	23.31		0		
	1	12	23.58	23.47	23.37	23.41	23.28	0	0		
	1	24	23.58	23.48	23.26	23.40	23.31		0		
QPSK	12	0	22.37	22.29	22.06	22.17	22.15		1		
	12	6	22.36	22.31	22.06	22.19	22.19	0-1	1		
	12	13	22.35	22.34	22.04	22.19	22.18	0-1	1		
	25	0	22.36	22.32	22.03	22.17	22.18		1		
	1	0	22.38	22.15	21.87	21.96	22.04		1		
	1	12	22.35	22.28	21.91	22.03	22.05	0-1	1		
	1	24	22.35	22.17	21.89	22.15	22.12	1	1		
16QAM	12	0	21.45	21.42	21.12	21.24	21.24		2		
	12	6	21.43	21.41	21.01	21.23	21.24	0-2	2		
	12	13	21.44	21.44	21.02	21.27	21.23	0-2	2		
	25	0	21.38	21.37	21.06	21.23	21.20		2		
	1	0	21.25	21.13	20.71	21.03	20.96		2		
	1	12	21.19	21.17	20.70	21.07	20.96	0-2	2		
	1	24	21.28	21.16	20.67	21.03	20.96		2		
64QAM	12	0	20.47	20.43	20.11	20.31	20.36		3		
	12	6	20.43	20.46	20.09	20.25	20.27	0-3	3		
	12	13	20.42	20.46	20.07	20.34	20.26	0-3	3		
	25	0	20.49	20.46	20.11	20.35	20.28		3		

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# k. LTE Band 41 - Power Class 2

**Table 8-41** LTE Band 41 (2593.0MHz) Conducted Powers – 20MHz Bandwidth

			Low Channel	Low-Mid Channel	Mid Channel	Mid-High Channel	High Channel		
Modulation	RB Size	RB Offset	39750 (2506.0 MHz)	40185 (2549.5 MHz)	40620 (2593.0 MHz)	41055 (2636.5 MHz)	41490 (2680.0 MHz)	MPR Allowed per 3GPP [dB]	MPR [dB]
				Co	nducted Power [dE	Bm]			
	1	0	26.06	26.27	26.33	25.79	26.02		0
	1	50	26.07	26.15	26.28	25.70	26.07	0	0
	1	99	26.11	26.00	26.23	25.79	25.96		0
QPSK	50	0	25.74	25.89	25.64	25.59	25.86		1
	50	25	25.70	25.92	25.55	25.56	25.78	0-1	1
	50	50	25.70	25.91	25.56	25.58	25.78	0-1	1
	100	0	25.75	25.97	25.62	25.50	25.78		1
	1	0	25.66	25.90	25.46	25.25	25.75		1
	1	50	25.84	25.88	25.40	25.39	25.71	0-1	1
	1	99	25.77	25.98	25.29	25.48	25.86		1
16QAM	50	0	24.97	24.96	24.80	24.65	24.96		2
	50	25	24.92	24.93	24.64	24.70	24.91	0-2	2
	50	50	24.92	24.87	24.73	24.70	24.85	0-2	2
	100	0	24.83	24.95	24.73	24.57	24.84		2
	1	0	24.44	24.57	24.14	24.58	24.56		2
	1	50	24.35	24.47	24.22	24.56	24.58	0-2	2
	1	99	24.41	24.55	23.87	24.59	24.48		2
64QAM	50	0	23.96	23.94	23.83	23.52	23.92		3
	50	25	23.90	23.97	23.78	23.54	23.81	0-3	3
	50	50	23.88	24.00	23.81	23.62	23.82	0-3	3
	100	0	23.87	23.97	23.73	23.70	23.91	7	3

**Table 8-42** LTE Band 41 (2593.0MHz) Conducted Powers – 15MHz Bandwidth

2.2 24.4 (2000.0										
			Low Channel	Low-Mid Channel	Mid Channel	Mid-High Channel	High Channel			
Modulation	RB Size	RB Offset	39750 (2506.0 MHz)	40185 (2549.5 MHz)	40620 (2593.0 MHz)	41055 (2636.5 MHz)	41490 (2680.0 MHz)	MPR Allowed per 3GPP [dB]	MPR [dB]	
			Conducted Power [dBm]							
	1	0	26.52	26.35	26.20	25.60	25.87		0	
	1	36	26.57	26.31	26.21	25.62	25.85	0	0	
	1	74	26.55	26.35	26.15	25.58	25.85		0	
QPSK	36	0	26.46	26.28	26.04	25.48	25.75		1	
	36	18	26.47	26.25	26.01	25.44	25.76	0-1	1	
	36	37	26.46	26.24	25.99	25.40	25.75	0-1	1	
	75	0	26.45	26.27	26.00	25.44	25.77		1	
	1	0	26.45	25.66	25.62	25.27	25.58		1	
	1	36	26.48	25.65	25.63	25.20	25.57	0-1	1	
	1	74	26.48	25.59	25.59	25.23	25.61		1	
16QAM	36	0	25.46	25.25	25.00	24.45	24.70		2	
	36	18	25.47	25.18	25.02	24.40	24.70	0-2	2	
	36	37	25.48	25.18	25.01	24.36	24.69	0-2	2	
	75	0	25.49	25.29	25.00	24.35	24.75		2	
	1	0	25.22	25.05	24.95	24.16	24.04		2	
	1	36	25.22	25.06	24.93	24.06	24.16	0-2	2	
	1	74	25.25	25.00	24.87	24.31	24.06		2	
64QAM	36	0	24.49	24.23	24.00	23.51	23.75		3	
	36	18	24.46	24.20	24.00	23.44	23.73	0-3	3	
	36	37	24.50	24.18	24.01	23.40	23.67	0-3	3	
	75	0	24.50	24.19	23.98	23.45	23.75		3	

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**Table 8-43** LTE Band 41 (2593.0MHz) Conducted Powers – 10MHz Bandwidth

			`		illaaotoa i				
			Low Channel	Low-Mid Channel	Mid Channel	Mid-High Channel	High Channel		
Modulation	RB Size	RB Offset	39750 (2506.0 MHz)	40185 (2549.5 MHz)	40620 (2593.0 MHz)	41055 (2636.5 MHz)	41490 (2680.0 MHz)	MPR Allowed per 3GPP [dB]	MPR [dB]
				Co	onducted Power [dE	ßm]			
	1	0	26.48	26.50	26.20	25.88	25.95		0
	1	25	26.51	26.45	26.16	25.80	25.89	0	0
	1	49	26.53	26.39	26.20	25.75	25.90		0
QPSK	25	0	26.39	26.29	26.06	25.48	25.76		1
	25	12	26.39	26.29	26.04	25.45	25.77	0-1	1
	25	25	26.34	26.21	26.03	25.42	25.76	0-1	1
	50	0	26.38	26.28	26.05	25.46	25.75		1
	1	0	26.15	25.90	25.95	25.29	25.40		1
	1	25	26.14	25.84	25.93	25.25	25.44	0-1	1
	1	49	26.14	25.82	25.89	25.25	25.45		1
16QAM	25	0	25.40	25.28	24.98	24.55	24.81		2
	25	12	25.35	25.24	24.97	24.52	24.82	0-2	2
	25	25	25.36	25.20	24.93	24.54	24.80	0-2	2
	50	0	25.45	25.32	25.11	24.44	24.77		2
	1	0	25.22	25.15	24.90	24.62	24.42		2
	1	25	25.26	25.14	24.97	24.56	24.41	0-2	2
	1	49	25.24	25.10	24.89	24.55	24.43		2
64QAM	25	0	24.40	24.30	24.11	23.60	23.85		3
	25	12	24.39	24.29	24.10	23.53	23.85	0-3	3
	25	25	24.39	24.27	24.07	23.50	23.81	0-3	3
	50	0	24.40	24.16	24.05	23.46	23.73		3

**Table 8-44** LTE Band 41 (2593.0MHz) Conducted Powers - 5MHz Bandwidth

	LTE Balla 41 (2595.0MHz) Collaucted Powers - 5MHz Ballawidti										
			Low Channel	Low-Mid Channel	Mid Channel	Mid-High Channel	High Channel				
Modulation	RB Size	RB Offset	39750 (2506.0 MHz)	40185 (2549.5 MHz)	40620 (2593.0 MHz)	41055 (2636.5 MHz)	41490 (2680.0 MHz)	MPR Allowed per 3GPP [dB]	MPR [dB]		
				Co	nducted Power [dB	m]					
	1	0	26.58	26.35	26.30	25.66	25.88		0		
	1	12	26.59	26.36	26.28	25.63	25.89	0	0		
	1	24	26.58	26.33	26.30	25.60	25.91		0		
QPSK	12	0	26.48	26.18	26.08	25.50	25.79		1		
	12	6	26.46	26.17	26.09	25.48	25.76	0-1	1		
	12	13	26.48	26.18	26.06	25.45	25.79	0-1	1		
	25	0	26.47	26.17	26.04	25.47	25.78		1		
	1	0	26.23	25.70	25.85	25.20	25.66		1		
	1	12	26.21	25.69	25.82	25.15	25.62	0-1	1		
	1	24	26.23	25.68	25.86	25.14	25.64		1		
16QAM	12	0	25.46	25.18	25.10	24.54	24.72		2		
	12	6	25.47	25.19	25.09	24.50	24.73	0-2	2		
	12	13	25.48	25.18	25.09	24.49	24.72	0-2	2		
	25	0	25.47	25.18	25.03	24.44	24.70		2		
	1	0	25.40	25.12	24.91	24.55	24.58		2		
	1	12	25.39	25.11	24.95	24.56	24.59	0-2	2		
	1	24	25.35	25.08	24.92	24.49	24.60		2		
64QAM	12	0	24.36	24.15	24.08	23.48	23.71		3		
	12	6	24.35	24.27	24.07	23.45	23.74	0-3	3		
	12	13	24.46	24.13	24.05	23.46	23.75	0-5	3		
	25	0	24.50	24.25	24.09	23.43	23.80		3		

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# VIII. WIFI Conducted Powers (SISO)

**Table 8-45** IEEE 802.11b/g/n (2.4GHz, SISO) Reduced Average RF Power<sup>1</sup>

	2.4GHz C	onducted Pov	ver [dBm]						
Eroa (MU=1	Channal	IEEE Transmission Mode							
Freq [MHz]	Channel	802.11b	802.11g	802.11n					
2412	1	14.87	14.84	14.90					
2437	6	14.85	14.89	14.76					
2462	11	14.84	14.93	14.66					

**Table 8-46** IEEE 802.11a/n/ac (5GHz, 20MHz BW, SISO) Reduced Average RF Power<sup>1</sup>

		) Conducted		Average i	
			Transmission	Mode	
Freq [MHz]	Channel	802.11a	802.11n	802.11ac	
5180	36	13.86	13.66	13.82	
5200	40	13.94	13.94	13.81	
5220	44	13.87	13.85	13.78	
5240	48	13.88	13.57	13.81	
5260	52	13.95	13.91	13.95	
5280	56	13.63	13.98	13.91	
5300	60	13.87	13.93	13.94	
5320	64	13.90	13.86	13.93	
5500	100	13.74	13.94	13.94	
5600	120	13.56	13.66	13.55	
5620	124	13.89	13.99	13.84	
5720	144	13.85	13.69	13.78	
5745	149	13.88	13.89	13.89	
5785	157	13.51	13.53	13.52	
5825	165	13.84	13.94	13.56	

**Table 8-47** IEEE 802.11n/ac (5GHz, 40MHz BW, SISO) Reduced Average RF Power<sup>1</sup>

5GHz	(40MHz) Cond	ducted Power	[dBm]		
			nission Mode		
Freq [MHz]	Channel	802.11n	802.11ac		
5190	38	13.87	13.91		
5230	46	13.90	13.92		
5270	54	13.94	13.95		
5310	62	13.98	13.95		
5510	102	13.87	13.94		
5590	118	13.74	13.70		
5630	126	13.94	13.65		
5710	142	13.57	13.80		
5755	151	13.87	13.53		
5795	159	13.51	13.59		

<sup>&</sup>lt;sup>1</sup> Note: This device utilizes independent power reduction mechanisms for the WIFI transmitter in 2.4GHz and 5GHz 20MHz and 40MHz modes for held-to-ear scenarios.

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**Table 8-48** IEEE 802.11ac (5GHz, 80MHz BW, SISO) Average RF Power

5GHz (80MH	lz) Conducted	Power [dBm]
Freq [MHz]	Channel	IEEE Transmission Mode
		802.11ac
5210	42	13.37
5290	58	12.42
5530	106	11.74
5610	122	12.71
5690	138	12.13
5775	155	12.19

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## 9. JUSTIFICATION OF HELD TO EAR MODES TESTED

# I. Analysis of RF Air Interface Technologies

An analysis was performed, following the guidance of §4.3 and §4.4 of the ANSI standard, of the RF air interface technologies being evaluated. The factors that will affect the RF interference potential were evaluated, and the worst-case operating modes were identified and used in the evaluation. A WD's interference potential is a function both of the WD's average near-field field strength and of the signal's audio-frequency amplitude modulation characteristics. Per §4.4, RF air interface technologies that have low power have been found to produce sufficiently low RF interference potential, so it is possible to exempt them from the product testing specified in Clause 5 of the ANSI standard. An RF air interface technology of a device is exempt from testing when its average antenna input power plus its MIF is ≤17dBm for all of its operating modes. RF air interface technologies exempted from testing in this manner are automatically assigned an M4 rating to be used in determining the overall rating for the WD.

The worst-case MIF plus the worst-case average antenna input power for all modes are investigated below to determine the testing requirements for this device.

## II. Individual Mode Evaluations

Table 9-1

Max Power + MIF calculations for Low Power Exemptions

Air Interface	Maximum Average Power (dBm)	Worst Case MIF (dB)	Total (Power + MIF, dB)	C63.19 Testing Required
CDMA - Full Frame Rate (RC1/SO55)	24.32	-14.70	9.62	No
CDMA - 1/8 <sup>th</sup> Frame Rate (RC1/SO3)	15.11*	2.99	18.10	Yes
CDMA - EvDO	24.54	-14.58	9.96	No
GSM850	23.62*	3.52	27.14	Yes
GSM1900	20.83*	3.50	24.33	Yes
EDGE850	17.67*	3.68	21.35	Yes**
EDGE1900	16.85*	4.03	20.88	Yes**
UMTS - RMC	25.00	-18.70	6.30	No
UMTS - AMR	25.00	-19.26	5.74	No
HSPA	19.85	-19.50	0.35	No
LTE - FDD	24.76	-9.43	15.33	No
LTE Band 41 - TDD (PC3)	13.99*	3.69	17.68	Yes
LTE Band 41 - TDD (PC2)	16.62*	3.79	20.41	Yes
2.4GHz WIFI	14.93	-4.02	10.88	No
5GHz WIFI	13.99	-4.10	9.89	No

<sup>\*</sup> Note: ANSI C63.19-2011 Sec. 4.4 Footnote 20 indicates the use of a long averaging time for measuring the antenna input power when using this method of exclusion. Therefore, the frame averaged power was calculated for these modes in this investigation.

## III. Low-Power Exemption Conclusions

Per ANSI C63.19-2011, RF Emissions testing for this device is required only for GSM/CDMA 1/8<sup>th</sup> Frame Rate voice modes as well as LTE TDD (Power Class 3 and Power Class 2) data modes. All other air interfaces are exempt.

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<sup>\*\*</sup> Note: EDGE data modes were considered but not tested as GSM voice modes were found to be the worst-case modes for the GSM air interface.

#### 10. LTE TDD UPLINK-DOWNLINK CONFIGURATION

# I. Uplink-Downlink Configuration Additional Testing

Additional testing was performed on each supported power class for LTE TDD to determine the worst-case Uplink-Downlink configuration for RFE testing.

Per 3GPP TS 36.211, the total frame length for each TDD radio frame of length  $T_f = 307200 \cdot T_s = 10$ ms, where T<sub>s</sub> is a number of time units equal to 1/(15000 x 2048) seconds. Additionally, each radio frame consists of 10 subframes, each of length  $30720 \cdot T_s = 1$  ms, and subframes can be designated as uplink (U), downlink (D), or special subframe (S), depending on the Uplink-Downlink configuration as indicated in Table 4.2-2 of 3GPP TS 36.211. In the transmission duty factor calculation, the special subframe configuration with the shortest UpPTS duration within the special subframe is used and will be applied for measurement. From 3GPP TS 36.211 Table 4.2-1, the shortest UpPTS is 2192 · Ts which occurs in the normal cyclic prefix and special subframe configuration 4.

See table below outlining the calculated transmission duty cycles for each Uplink-Downlink configuration:

> **Table 10-1** Unlink-Downlink Configurations for Type 2 Frame Structures

Uplink-downlink configuration	Downlink-to-Uplink Switch-point periodicity				Calculated Transmission							
configuration	Switch-point periodicity	0	1	2	3	4	5	6	7	8	9	Duty Cycle (%)
0	5 ms	D	S	U	U	U	D	S	U	U	U	61.4%
1	5 ms	D	S	U	U	D	D	S	U	U	D	41.4%
2	5 ms	D	S	U	D	D	D	S	U	D	D	21.4%
3	10 ms	D	S	U	U	U	D	D	D	D	D	30.7%
4	10 ms	D	S	U	U	D	D	D	D	D	D	20.7%
5	10 ms	D	S	U	D	D	D	D	D	D	D	10.7%
6	5 ms	D	S	U	U	U	D	S	U	U	D	51.4%

# II. Power Class 3 Uplink-Downlink Configuration Additional Testing

LTE TDD was evaluated with the following radio configuration: channel 40620, 20MHz BW, 16QAM, 1RB, 0RB Offset. For Power Class 3, all configurations (0-6) are supported. The configuration which resulted in the worst-case emission was used for full testing. See Table 10-2 below for results. The configuration determined in the results below was used to measure the MIF values in Table 7-5.

> **Table 10-2** LTF TDD Power Class 3 UL-DL Configuration Results

				_ ' L	טטו	1 00	ici Cias	3 J UL	DL 001	myurat	0111169	uito			
Mode / Band	Bandwidth	Channel	UL-DL Config.	Mod.	RB Size	RB Offset	Scan Center	Time Avg. Field (V/m)	Time Avg. Field [dB(V/m)]	MIF (dB)	Audio Interference Level [dB(V/m)]	FCC Limit (dBV/m)	FCC Margin (dB)	Result	Excl Blocks per 5.5
E-Field Emission	E-Field Emissions														
	20	40620	0	16QAM	1	0	Acoustic	20.00	26.02	-3.25	22.77	35.00	-12.23	M4	none
	20	40620	1	16QAM	1	0	Acoustic	16.17	24.17	-1.56	22.61	35.00	-12.39	M4	none
	20	40620	2	16QAM	1	0	Acoustic	12.64	22.03	1.52	23.55	35.00	-11.45	M4	none
LTE TDD / Band 41	20	40620	3	16QAM	1	0	Acoustic	15.02	23.53	-1.37	22.16	35.00	-12.84	M4	none
	20	40620	4	16QAM	1	0	Acoustic	12.81	22.15	0.76	22.91	35.00	-12.09	M4	none
	20	40620	5	16QAM	1	0	Acoustic	10.15	20.13	3.68	23.81	35.00	-11.19	M4	none
	20	40620	6	16QAM	1	0	Acoustic	17.95	25.08	-2.40	22.68	35.00	-12.32	M4	none

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# III. Power Class 2 Uplink-Downlink Configuration Additional Testing

LTE TDD was evaluated with the following radio configuration: channel 40620, 20MHz BW, 16QAM, 1RB, 0RB Offset. For Power Class 2, only configurations 1-5 are supported. The configuration which resulted in the worst-case emission was used for full testing. See Table 10-3 below for results. The configuration determined in the results below was used to measure the MIF values in Table 7-6.

> **Table 10-3** LTE TDD Power Class 2 UL-DL Configuration Results

Mode / Band	Bandwidth	Channel	UL-DL Config.	Mod.	RB Size	RB Offset	Scan Center	Time Avg. Field (V/m)	Time Avg. Field [dB(V/m)]	MIF (dB)	Audio Interference Level [dB(V/m)]	FCC Limit (dBV/m)	FCC Margin (dB)	Result	Excl Blocks per 5.5
E-Field Emission	ons														
	20	40620	1	16QAM	1	0	Acoustic	17.09	24.65	-1.52	23.13	35.00	-11.87	M4	none
	20	40620	2	16QAM	1	0	Acoustic	12.90	22.21	1.50	23.71	35.00	-11.29	M4	none
LTE TDD / Band 41	20	40620	3	16QAM	1	0	Acoustic	15.42	23.76	-1.30	22.46	35.00	-12.54	M4	none
	20	40620	4	16QAM	1	0	Acoustic	13.51	22.61	0.67	23.28	35.00	-11.72	M4	none
	20	40620	5	16QAM	1	0	Acoustic	10.52	20.44	3.73	24.17	35.00	-10.83	M4	none

## **IV. Conclusion**

Per the results above, UL-DL Configuration 5 was used for both LTE TDD Power Class 3 and LTE TDD Power Class 2 testing.

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#### **OVERALL MEASUREMENT SUMMARY** 11.

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## I. E-FIELD EMISSIONS:

## **Table 11-1 HAC Data Summary for CDMA E-field**

	Three Bata Sammary for Spinkt 2 mola												
Mode	Channel	RC/SO	DUT SN	Scan Center	Conducted Power at BS (dBm)	Time Avg. Field (V/m)	Time Avg. Field [dB(V/m)]	MIF (dB)	Audio Interference Level [dB(V/m)]	FCC Limit (dBV/m)	FCC Margin (dB)	Result	Excl Blocks per 5.5
E-Field Emission	ons												
	564*	RC1/SO3	12726	Acoustic	24.06	18.82	25.49	2.93	28.42	45.00	-16.58	M4	none
Cellular CDMA	1013	RC1/SO3	12726	Acoustic	24.14	18.61	25.39	2.90	28.29	45.00	-16.71	M4	none
Cellular CDIVIA	384	RC1/SO3	12726	Acoustic	24.12	19.74	25.91	2.89	28.80	45.00	-16.20	M4	none
	777	RC1/SO3	12726	Acoustic	23.67	16.44	24.32	2.95	27.27	45.00	-17.73	M4	none
	25	RC1/SO3	12726	Acoustic	23.48	11.52	21.23	2.85	24.08	35.00	-10.92	M4	none
PCS CDMA	600	RC1/SO3	12726	Acoustic	23.54	11.63	21.31	2.81	24.12	35.00	-10.88	M4	none
	1175	RC1/SO3	12726	Acoustic	23.54	10.58	20.49	2.99	23.48	35.00	-11.52	M4	none

\*Note: Cell. CDMA Ch. 564 is the Part 90S test channel.

## **Table 11-2 HAC Data Summary for GSM E-field**

	TIAO Data Gaininary for Goin E-ficia											
Mode	Channel	DUT SN	Scan Center	Conducted Power at BS (dBm)	Time Avg. Field (V/m)	Time Avg. Field [dB(V/m)]	MIF (dB)	Audio Interference Level [dB(V/m)]	FCC Limit (dBV/m)	FCC Margin (dB)	Result	Excl Blocks per 5.5
E-Field Emissions												
	128	12726	Acoustic	32.39	45.24	33.11	3.52	36.63	45.00	-8.37	M4	none
GSM850	190	12726	Acoustic	32.61	38.39	31.68	3.52	35.20	45.00	-9.80	M4	none
	251	12726	Acoustic	32.65	42.65	32.60	3.52	36.12	45.00	-8.88	M4	none
	512	12726	Acoustic	29.86	21.29	26.57	3.50	30.07	35.00	-4.93	М3	none
GSM1900	661	12726	Acoustic	29.42	20.40	26.19	3.50	29.69	35.00	-5.31	M4	none
G3W1900	810	12726	Acoustic	29.28	19.77	25.92	3.50	29.42	35.00	-5.58	M4	none
	512	12726	T-Coil	29.86	19.39	25.75	3.50	29.25	35.00	-5.75	M4	none

## **Table 11-3** HAC Data Summary for LTF TDD B41 (PC3) F-field

	TIAO Data Sullillary for LTL 100 D41 (1 03) L-field															
Mode / Band	Bandwidth	Channel	DUT SN	UL-DL Config.	Mod.	RB Size	RB Offset	Scan Center	Time Avg. Field (V/m)	Time Avg. Field [dB(V/m)]	MIF (dB)	Audio Interference Level [dB(V/m)]	FCC Limit (dBV/m)	FCC Margin (dB)	Result	Excl Blocks per 5.5
E-Field Emission	ons															
	10	39750	10223	5	16QAM	1	0	Acoustic	11.58	21.27	3.64	24.91	35.00	-10.09	M4	none
	10	40185	10223	5	16QAM	1	0	Acoustic	12.05	21.62	3.61	25.23	35.00	-9.77	M4	none
LTE TDD / Band 41 PC3	10	40620	10223	5	16QAM	1	0	Acoustic	11.87	21.49	3.69	25.18	35.00	-9.82	M4	none
	10	41055	10223	5	16QAM	1	0	Acoustic	11.96	21.55	3.67	25.22	35.00	-9.78	M4	none
	10	41490	10223	5	16QAM	1	0	Acoustic	10.74	20.62	3.65	24.27	35.00	-10.73	M4	none

## **Table 11-4** HAC Data Summary for LTE TDD B41 (PC2) E-field

				, .,			<i>-</i>	u.y			, ,,	,					
Mode / Band	Bandwidth	Channel	DUT SN	UL-DL Config.	Mod.	RB Size	RB Offset	Scan Center	Conducted Power at BS (dBm)	Time Avg. Field (V/m)	Time Avg. Field [dB(V/m)]	MIF (dB)	Audio Interference Level [dB(V/m)]	FCC Limit (dBV/m)	FCC Margin (dB)	Result	Excl Blocks per 5.5
E-Field Emission	ons																
	20	39750	10223	5	64QAM	1	0	Acoustic	24.44	12.61	22.01	3.72	25.73	35.00	-9.27	M4	none
	20	40185	10223	5	64QAM	1	0	Acoustic	24.57	13.05	22.31	3.65	25.96	35.00	-9.04	M4	none
LTE TDD / Band 41 PC2	20	40620	10223	5	64QAM	1	0	Acoustic	24.14	12.77	22.12	3.75	25.87	35.00	-9.13	M4	none
	20	41055	10223	5	64QAM	1	0	Acoustic	24.58	12.72	22.09	3.71	25.80	35.00	-9.20	M4	none
	20	41490	10223	5	64QAM	1	0	Acoustic	24.56	11.93	21.53	3.79	25.32	35.00	-9.68	M4	none

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# II. Worst-case Configuration Evaluation

**Table 11-5** Peak Reading 360° Probe Rotation at Azimuth axis

Mode	Channel	DUT SN	Scan Center	Time Avg. Field (V/m)	Time Avg. Field [dB(V/m)]	MIF (dB)	Audio Interference Level [dB(V/m)]	FCC Limit (dBV/m)	FCC Margin (dB)	Result	Excl Blocks per 5.5
Probe Rotation	Probe Rotation at Worst-Case										
GSM1900	512	12726	Acoustic	22.31	26.97	3.50	30.47	35.00	-4.53	М3	none

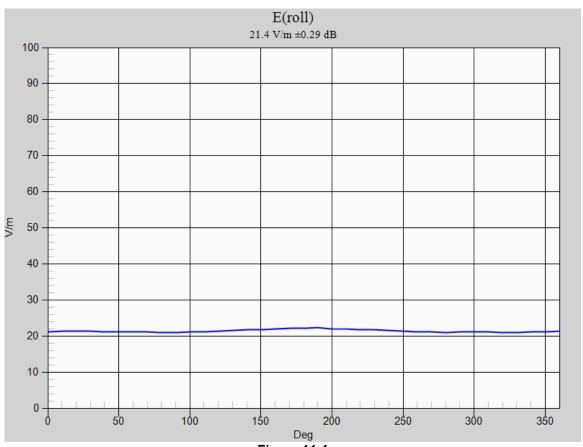


Figure 11-1 **Worst-Case Probe Rotation about Azimuth axis** 

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<sup>\*</sup> Note: Locations of probe rotation (with and without exclusions) are shown in Figure 11-2 denoted by the green square markers.

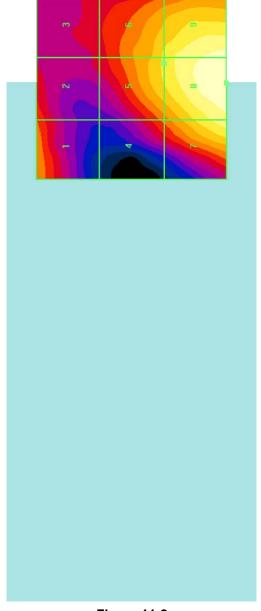


Figure 11-2
Sample E-field Scan Overlay
(See Test Setup Photographs for actual WD overlay)

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#### **EQUIPMENT LIST** 12.

## **Table 12-1 Equipment List**

Manufacturer	Model	Description Description	Cal Date	Cal Interval	Cal Due	Serial Number
Agilent	E5515C	8960 Series 10 Wireless Communications Test Set	12/18/2018	Annual	12/18/2019	GB42230325
	N5182A					
Agilent		MXG Vector Signal Generator	11/28/2018	Annual	11/28/2019	
Agilent	E4438C	ESG Vector Signal Generator	3/11/2019	Biennial	3/11/2021	MY45090700
Amplifier Research	15S1G6	Amplifier	N/A	CBT*	N/A	433978
Anritsu	ML2496A	Power Meter	10/21/2018	Annual	10/21/2019	1138001
Anritsu	MA2411B	Pulse Power Sensor	11/20/2018	Annual	11/20/2019	1339007
Anritsu	MA2411B	Pulse Power Sensor	11/20/2018	Annual	11/20/2019	1339008
Anritsu	MA24106A	USB Power Sensor	1/31/2019	Annual	1/31/2020	1520503
Anritsu	MA24106A	USB Power Sensor	1/31/2019	Annual	1/31/2020	1520501
Control Company	4040	Temperature / Humidity Monitor	2/28/2018	Biennial	2/28/2020	150761911
Mini-Circuits	NLP-1200+	Low Pass Filter DC to 1000 MHz	N/A	CBT*	N/A	N/A
Mini-Circuits	NLP-2950+	Low Pass Filter DC to 2700 MHz	N/A	CBT*	N/A	N/A
Mini-Circuits	BW-N20W5	Power Attenuator	N/A	CBT*	N/A	1226
Pasternack	PE2237-20	Bidirectional Coupler	N/A	CBT*	N/A	N/A
Rohde & Schwarz	CMW500	Radio Communication tester	8/3/2018	Annual	8/3/2019	140144
Rohde & Schwarz	CMW500	Wideband Radio Communication Tester	1/30/2019	Annual	1/30/2020	162125
Seekonk	NC-100	Torque Wrench (8" lb)	5/23/2018	Biennial	5/23/2020	N/A
SPEAG	AIA	Audio Interference Analzyer	N/A	CBT*	N/A	1010
SPEAG	EF3DV3	Freespace E-field Probe	1/16/2019	Annual	1/16/2020	4035
SPEAG	DAE4	Dasy Data Acquisition Electronics	3/13/2019	Annual	3/13/2020	1415
SPEAG	CD835V3	Freespace 835 MHz Dipole	2/19/2019	Biennial	2/19/2021	1003
SPEAG	CD1880V3	Freespace 1880 MHz Dipole	2/19/2019	Biennial	2/19/2021	1137
SPEAG	CD2600V3	Freespace 2600MHz Dipole	2/19/2019	Biennial	2/19/2021	1012

Calibration traceable to the National Institute of Standards and Technology (NIST).

\*Note: CBT (Calibrated Before Testing). Prior to testing, the measurement paths containing a cable, attenuator, coupler or filter were connected to a calibrated source (i.e. a signal generator) to determine the losses of the measurement path. The power meter offset was then adjusted to compensate for the measurement system losses. This level offset is stored within the power meter before measurements are made. This calibration verification procedure applies to the system verification and output power measurements. The calibrated reading is then taken directly from the power meter after compensation of the losses for all final power measurements.

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#### 13. **MEASUREMENT UNCERTAINTY**

## **Table 13-1 Uncertainty Estimation Table**

Wireless Communications Device Near-Field Measurement Uncertainty Estimation							
Uncertainty Component	Data (dB)	Data Type	Prob. Dist.	Divisor	Ci (E)	Unc. (dB)	Notes/Comments
Measurement System	•					*	
RF System Reflections	0.50	Tolerance	N	1.00	1	0.50	* Refl. < -20 dB
Field Probe Calibration	0.21	Tolerance	N	1.00	1	0.21	
Field Probe Isotropy	0.01	Tolerance	N	1.00	1	0.01	
Field Probe Frequency Response	0.135	Tolerance	N	1.00	1	0.14	
Field Probe Linearity	0.013	Tolerance	N	1.00	1	0.01	
Modulation Interference Factor	0.20	Tolerance	R	1.73	1	0.12	Applicable for M-rating testing
Boundary Effects	0.105	Accuracy	R	1.73	1	0.06	*
Probe Positioning Accuracy	0.20	Accuracy	R	1.73	1	0.12	*
Probe Positioner	0.050	Accuracy	R	1.73	1	0.03	*
Extrapolation/Interpolation	0.045	Tolerance	R	1.73	1	0.03	*
Resolution to 2mm error	0.21	Tolerance	N	1.00	1	0.21	
System Detection Limit	0.05	Tolerance	R	1.73	1	0.03	*
Readout Electronics	0.015	Tolerance	N	1.00	1	0.02	*
Integration Time	0.11	Tolerance	R	1.73	1	0.06	*
Response Time	0.033	Tolerance	R	1.73	1	0.02	*
Phantom Thickness	0.10	Tolerance	R	1.73	1	0.06	*
System Repeatability (Field x 2=power)	0.17	Tolerance	N	1.00	1	0.17	*
Test Sample Related	-						
Device Positioning Vertical	0.2	Tolerance	R	1.73	1	0.12	*
Device Positioning Lateral	0.045	Tolerance	R	1.73	1	0.03	*
Device Holder and Phantom	0.1	Tolerance	R	1.73	1	0.06	*
Power Drift	0.21	Tolerance	R	1.73	1	0.12	
Combined Standard Uncertainty (k=1)					0.66	16.3%	
Expanded Uncertainty [95% confidence]					1.31	32.6%	
Expanded Uncertainty [95% confidence]	on Field					0.66	16.3%

#### Notes:

- Test equipments are calibrated according to techniques outlined in NIS81, NIS3003 and NIST Tech Note 1297, All equipments have traceability according to NIST. Measurement Uncertainties are defined in further detail in NIS 81 and NIST Tech Note 1297 and UKAS M3003.
- \* Uncertainty specifications from Schmidt & Partner Engineering AG (not site specific) 2.

Measurement uncertainty reflects the quality and accuracy of a measured result as compared to the true value. Such statements are generally required when stating results of measurements so that it is clear to the intended audience that the results may differ when reproduced by different facilities. Measurement results vary due to the measurement uncertainty of the instrumentation, measurement technique, and test engineer. Most uncertainties are calculated using the tolerances of the instrumentation used in the measurement, the measurement setup variability, and the technique used in performing the test. While not generally included, the variability of the equipment under test also figures into the overall measurement uncertainty. Another component of the overall uncertainty is based on the variability of repeated measurements (so-called Type A uncertainty). This may mean that the Hearing Aid immunity tests may have to be repeated by taking down the test setup and resetting it up so that there are a statistically significant number of repeat measurements to identify the measurement uncertainty. By combining the repeat measurement results with that of the instrumentation chain using the technique contained in NIS 81 and NIS 3003, the overall measurement uncertainty was estimated.

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# 14. TEST DATA

See following Attached Pages for Test Data.

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## DUT: CD835V3 - SN1003

Type: CD835V3 Serial: 1003

#### Communication System: CW; Frequency: 835 MHz;

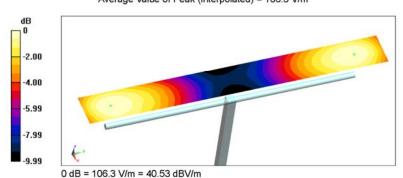
Measurement Standard: DASY5 (IEEE/IEC/ANSI C63.19-2011)

#### DASY5 Configuration:

- Probe: EF3DV3 SN4035; Calibrated: 1/16/2019;
- Sensor-Surface: 0mm (Fix Surface)
- Electronics: DAE4 Sn1415; Calibrated: 3/13/2019
- Phantom: HAC Test Arch with AMCC; Type: SD HAC P01 BA;
- Measurement SW: DASY52, Version 52.10 (0);

#### 835 MHz / 100mW HAC Dipole Validation at 15mm/Hearing Aid Compatibility Test (41x361x1):

Interpolated grid: dx=0.5000 mm, dy=0.5000 mm Device Reference Point: 0, 0, -6.3 mm Reference Value = 128.0 V/m; Power Drift = -0.03 dB Applied MIF = 0.00 dB Average Value of Peak (interpolated) = 106.3 V/m



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#### **DUT: CD1880V3 - SN1137**

Type: CD1880V3 Serial: 1137

#### Communication System: CW; Frequency: 1880 MHz;

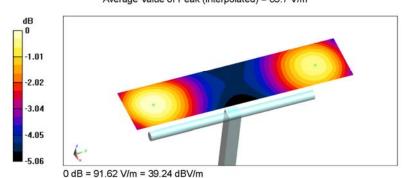
Measurement Standard: DASY5 (IEEE/IEC/ANSI C63.19-2011)

#### DASY5 Configuration:

- Probe: EF3DV3 SN4035; Calibrated: 1/16/2019;
- Sensor-Surface: 0mm (Fix Surface)
- Electronics: DAE4 Sn1415; Calibrated: 3/13/2019
- Phantom: HAC Test Arch with AMCC; Type: SD HAC P01 BA;
- Measurement SW: DASY52, Version 52.10 (0);

#### 1880 MHz / 100mW HAC Dipole Validation at 15mm/Hearing Aid Compatibility Test (41x181x1):

Interpolated grid: dx=0.5000 mm, dy=0.5000 mm Device Reference Point: 0, 0, -6.3 mm Reference Value = 153.8 V/m; Power Drift = 0.07 dB Applied MIF = 0.00 dB Average Value of Peak (interpolated) = 89.7 V/m



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## DUT: CD2600V3 - SN1012

Type: CD2600V3 Serial: 1012

#### Communication System: CW; Frequency: 2600 MHz;

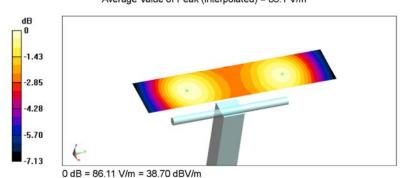
Measurement Standard: DASY5 (IEEE/IEC/ANSI C63.19-2011)

#### DASY5 Configuration:

- Probe: EF3DV3 SN4035; Calibrated: 1/16/2019;
- Sensor-Surface: 0mm (Fix Surface)
- Electronics: DAE4 Sn1415; Calibrated: 3/13/2019
- Phantom: HAC Test Arch with AMCC; Type: SD HAC P01 BA;
- Measurement SW: DASY52, Version 52.10 (0);

#### 2600 MHz / 100mW HAC Dipole Validation at 15mm/Hearing Aid Compatibility Test (41x181x1):

Interpolated grid: dx=0.5000 mm, dy=0.5000 mm Device Reference Point: 0, 0, -6.3 mm Reference Value = 67.82 V/m; Power Drift = 0.03 dB Applied MIF = 0.00 dB Average Value of Peak (interpolated) = 85.1 V/m



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Date: 5/1/2019



## DUT: A3LSMA102U

Type: Portable Handset Serial: 12726 Backlight off Duty Cycle: 1:8

#### Communication System: CDMA; Frequency: 836.52 MHz;

Measurement Standard: DASY5 (IEEE/IEC/ANSI C63.19-2011)

#### DASY5 Configuration:

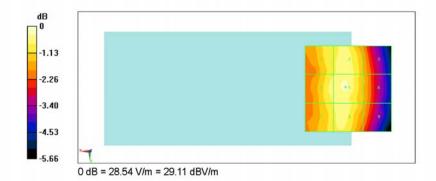
- Probe: EF3DV3 SN4035; Calibrated: 1/16/2019;
- Sensor-Surface: (Fix Surface)
- Electronics: DAE4 Sn1415: Calibrated: 3/13/2019
- Phantom: HAC Test Arch with AMCC; Type: SD HAC P01 BA;
- Measurement SW: DASY52, Version 52.10 (0);

#### Cellular CDMA Mid Channel/Hearing Aid Compatibility Test (101x101x1):

Interpolated grid: dx=0.5000 mm, dy=0.5000 mm Device Reference Point: 0, 0, -6.3 mm Reference Value = 26.72 V/m; Power Drift = -0.11 dB Applied MIF = 2.89 dB RF audio interference level = 28.80 dBV/m Emission category: M4

#### MIF scaled E-field

Grid 1 M4	Grid 2 M4	Grid 3 M4
28.31 dBV/m	28.61 dBV/m	27.68 dBV/m
Grid 4 M4	Grid 5 M4	Grid 6 M4
28.59 dBV/m	28.8 dBV/m	27.75 dBV/m
Grid 7 M4	Grid 8 M4	Grid 9 M4



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Date: 5/1/2019



#### DUT: A3LSMA102U

Type: Portable Handset Serial: 12726 Backlight off Duty Cycle: 1:8

#### Communication System: CDMA; Frequency: 1880 MHz;

Measurement Standard: DASY5 (IEEE/IEC/ANSI C63.19-2011)

#### DASY5 Configuration:

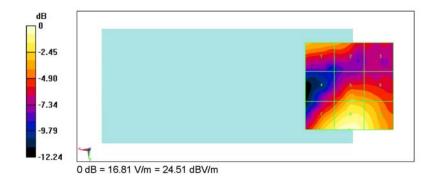
- Probe: EF3DV3 SN4035; Calibrated: 1/16/2019;
- Sensor-Surface: (Fix Surface)
- Electronics: DAE4 Sn1415; Calibrated: 3/13/2019
- Phantom: HAC Test Arch with AMCC; Type: SD HAC P01 BA;
- Measurement SW: DASY52, Version 52.10 (0);

#### PCS CDMA Mid Channel/Hearing Aid Compatibility Test (101x101x1):

Interpolated grid: dx=0.5000 mm, dy=0.5000 mm Device Reference Point: 0, 0, -6.3 mm Reference Value = 8.063 V/m; Power Drift = 0.16 dB Applied MIF = 2.81 dB RF audio interference level = 24.12 dBV/m Emission category: M4

### MIF scaled E-field

Grid 1 M4	Grid 2 M4	Grid 3 M4
21.54 dBV/m	20.97 dBV/m	18.76 dBV/m
Grid 4 M4	Grid 5 M4	Grid 6 M4
18.95 dBV/m	21.62 dBV/m	21.12 dBV/m
Grid 7 M4	Grid 8 M4	Grid 9 M4
23.19 dBV/m	24.12 dBV/m	23.38 dBV/m



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## DUT: A3LSMA102U

Type: Portable Handset Serial: 12726 Backlight off Duty Cycle: 1:8.3

#### Communication System: GSM; Frequency: 824.2 MHz;

Measurement Standard: DASY5 (IEEE/IEC/ANSI C63.19-2011)

#### DASY5 Configuration:

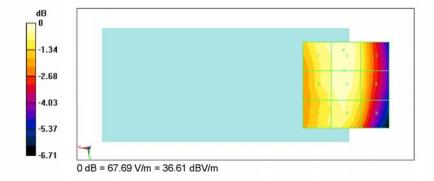
- Probe: EF3DV3 SN4035; Calibrated: 1/16/2019;
- Sensor-Surface: (Fix Surface)
- Electronics: DAE4 Sn1415; Calibrated: 3/13/2019
- Phantom: HAC Test Arch with AMCC; Type: SD HAC P01 BA;
- Measurement SW: DASY52, Version 52.10 (0);

#### GSM850 Low Channel/Hearing Aid Compatibility Test (101x101x1):

Interpolated grid: dx=0.5000 mm, dy=0.5000 mm Device Reference Point: 0, 0, -6.3 mm Reference Value = 59.77 V/m; Power Drift = 0.14 dB Applied MIF = 3.52 dB RF audio interference level = 36.63 dBV/m Emission category: M4

### MIF scaled E-field

Grid 1 M4	Grid 2 M4	Grid 3 M4
36.33 dBV/m	36.63 dBV/m	35.7 dBV/m
Grid 4 M4	Grid 5 M4	Grid 6 M4
36.22 dBV/m	36.51 dBV/m	35.63 dBV/m
Grid 7 <b>M4</b>	Grid 8 M4	Grid 9 M4
35.87 dBV/m	36.24 dBV/m	35.24 dBV/m



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#### DUT: A3LSMA102U

Type: Portable Handset Serial: 12726 Backlight off Duty Cycle: 1:8.3

#### Communication System: GSM; Frequency: 1850.2 MHz;

Measurement Standard: DASY5 (IEEE/IEC/ANSI C63.19-2011)

#### DASY5 Configuration:

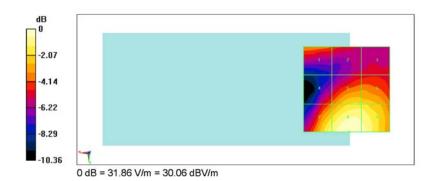
- Probe: EF3DV3 SN4035; Calibrated: 1/16/2019;
- Sensor-Surface: (Fix Surface)
- Electronics: DAE4 Sn1415; Calibrated: 3/13/2019
- Phantom: HAC Test Arch with AMCC; Type: SD HAC P01 BA;
- Measurement SW: DASY52, Version 52.10 (0);

#### GSM1900 Low Channel/Hearing Aid Compatibility Test (101x101x1):

Interpolated grid: dx=0.5000 mm, dy=0.5000 mm Device Reference Point: 0, 0, -6.3 mm Reference Value = 17.40 V/m; Power Drift = 0.14 dB Applied MIF = 3.50 dB RF audio interference level = 30.07 dBV/m Emission category: M3

### MIF scaled E-field

Grid 1 M4	Grid 2 M4	Grid 3 M4
26.63 dBV/m	26.01 dBV/m	25.17 dBV/m
Grid 4 M4	Grid 5 M4	Grid 6 M4
26.27 dBV/m	28.17 dBV/m	28.16 dBV/m
Grid 7 M4	Grid 8 M3	Grid 9 M4
29.2 dBV/m	30.07 dBV/m	29.67 dBV/m



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## DUT: A3LSMA102U

Type: Portable Handset Serial: 10223 Backlight off Duty Cycle: 1:9.35

## Communication System: LTE TDD41; Frequency: 2549.5 MHz;

Measurement Standard: DASY5 (IEEE/IEC/ANSI C63.19-2011)

#### DASY5 Configuration:

- Probe: EF3DV3 SN4035; Calibrated: 1/16/2019;
- Sensor-Surface: (Fix Surface)
- Electronics: DAE4 Sn1415; Calibrated: 3/13/2019
- Phantom: HAC Test Arch with AMCC; Type: SD HAC P01 BA;
- Measurement SW: DASY52, Version 52.10 (0);

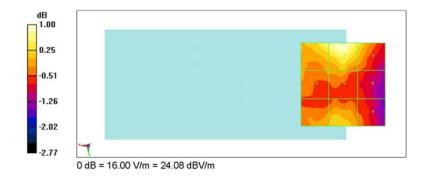
#### PC3 TDD LTE Band 41 Low Mid Channel, UL-DL 5, 10MHz, 16QAM, 1RB, 0 RB Offset,

#### Hearing Aid Compatibility Test (101x101x1):

Interpolated grid: dx=0.5000 mm, dy=0.5000 mm Device Reference Point: 0, 0, -6.3 mm Reference Value = 11.55 V/m; Power Drift = 0.15 dB Applied MIF = 3.61 dB RF audio interference level = 25.23 dBV/m Emission category: M4

#### MIF scaled E-field

Grid 1 M4	Grid 2 M4	Grid 3 M4
24.83 dBV/m	25.23 dBV/m	24.52 dBV/m
Grid 4 M4	Grid 5 M4	Grid 6 M4
23.98 dBV/m	24.09 dBV/m	23.63 dBV/m
Grid 7 <b>M4</b>	Grid 8 M4	Grid 9 M4
24.08 dBV/m	24.24 dBV/m	23.8 dBV/m



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Date: 5/1/2019



## **DUT: A3LSMA102U**

Type: Portable Handset Serial: 10223 Backlight off Duty Cycle: 1:9.35

## Communication System: LTE TDD41; Frequency: 2549.5 MHz;

Measurement Standard: DASY5 (IEEE/IEC/ANSI C63.19-2011)

#### DASY5 Configuration:

- Probe: EF3DV3 SN4035; Calibrated: 1/16/2019;
- Sensor-Surface: (Fix Surface)
- Electronics: DAE4 Sn1415; Calibrated: 3/13/2019
- Phantom: HAC Test Arch with AMCC; Type: SD HAC P01 BA;
- Measurement SW: DASY52, Version 52.10 (0);

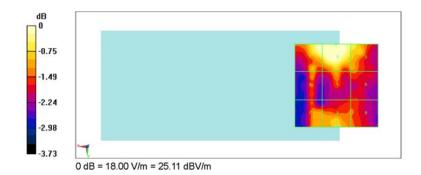
#### PC2 TDD LTE Band 41 Low Mid Channel, UL-DL 5, 20MHz, 64QAM, 1RB, 0RB Offset,

#### Hearing Aid Compatibility Test (101x101x1):

Interpolated grid: dx=0.5000 mm, dy=0.5000 mm Device Reference Point: 0, 0, -6.3 mm Reference Value = 10.22 V/m; Power Drift = 0.10 dB Applied MIF = 3.65 dB RF audio interference level = 25.96 dBV/m Emission category: M4

#### MIF scaled E-field

Grid 1	M4	Grid 2	M4	Grid 3	M4
25.22	dBV/m	25.96	dBV/m	24.69	dBV/m
Grid 4	M4	Grid 5	M4	Grid 6	M4
23.97	dBV/m	24.01	dBV/m	23.76	dBV/m
Grid 7	M4	Grid 8	M4	Grid 9	M4
24.08	dBV/m	24.32	dBV/m	23.77	dBV/m



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#### CALIBRATION CERTIFICATES 15.

The following pages include the probe calibration used to evaluate HAC for the DUT.

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## Calibration Laboratory of

Schmid & Partner Engineering AG Zeughausstrasse 43, 8004 Zurich, Switzerland





Schweizerischer Kalibrierdienst Service suisse d'étalonnage

Service suisse d'étalonnage
Servizio svizzero di taratura
Swiss Calibration Service

Accreditation No.: SCS 0108

Accredited by the Swiss Accreditation Service (SAS)
The Swiss Accreditation Service is one of the signatories to the EA
Multilateral Agreement for the recognition of calibration certificates

Client

PC Test

Certificate No: EF3-4035\_Jan19

# **CALIBRATION CERTIFICATE**

Object

EF3DV3-SN:4035

Calibration procedure(s)

QA CAL-02.v9, QA CAL-25.v7

Calibration procedure for E-field probes optimized for close near field

evaluations in air

Calibration date:

January 16, 2019

2/1/2019

This calibration certificate documents the traceability to national standards, which realize the physical units of measurements (SI). The measurements and the uncertainties with confidence probability are given on the following pages and are part of the certificate.

All calibrations have been conducted in the closed laboratory facility: environment temperature  $(22 \pm 3)^{\circ}$ C and humidity < 70%.

Calibration Equipment used (M&TE critical for calibration)

Primary Standards	ID	Cal Date (Certificate No.)	Scheduled Calibration
Power meter NRP	SN: 104778	04-Apr-18 (No. 217-02672/02673)	Apr-19
Power sensor NRP-Z91	SN: 103244	04-Apr-18 (No. 217-02672)	Apr-19
Power sensor NRP-Z91	SN: 103245	04-Apr-18 (No. 217-02673)	Apr-19
Reference 20 dB Attenuator	SN: S5277 (20x)	04-Apr-18 (No. 217-02682)	Apr-19
DAE4	SN: 789	14-Jan-19 (No. DAE4-789_Jan19)	Jan-20
Reference Probe ER3DV6	SN: 2328	09-Oct-18 (No. ER3-2328_Oct18)	Oct-19
Secondary Standards	ID	Check Date (in house)	Scheduled Check
Power meter E4419B	SN: GB41293874	06-Apr-16 (in house check Jun-18)	In house check: Jun-20
Power sensor E4412A	SN: MY41498087	06-Apr-16 (in house check Jun-18)	In house check; Jun-20
Power sensor E4412A	SN: 000110210	06-Apr-16 (in house check Jun-18)	In house check: Jun-20
RF generator HP 8648C	SN: US3642U01700	04-Aug-99 (in house check Jun-18)	In house check: Jun-20
Network Analyzer E8358A	SN: US41080477	31-Mar-14 (in house check Oct-18)	In house check; Oct-19

Calibrated by:

Name
Function
Signature
Laboratory Technician

Approved by:

Katja Pokovic
Technical Manager

Issued: January 17, 2019

This calibration certificate shall not be reproduced except in full without written approval of the laboratory.

Certificate No: EF3-4035\_Jan19

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## Calibration Laboratory of

Schmid & Partner Engineering AG Zeughausstrasse 43, 8004 Zurich, Switzerland





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Swiss Calibration Service

Accreditation No.: SCS 0108

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Glossary:

NORMx,y,z sensitivity in free space DCP diode compression point

CF crest factor (1/duty\_cycle) of the RF signal
A, B, C, D modulation dependent linearization parameters
En incident E-field orientation normal to probe axis
Ep incident E-field orientation parallel to probe axis

Polarization φ rotation around probe axis

Polarization 9 9 rotation around an axis that is in the plane normal to probe axis (at measurement center),

i.e.,  $\vartheta = 0$  is normal to probe axis

Connector Angle information used in DASY system to align probe sensor X to the robot coordinate system

## Calibration is Performed According to the Following Standards:

 IEEE Std 1309-2005, "IEEE Standard for calibration of electromagnetic field sensors and probes, excluding antennas, from 9 kHz to 40 GHz", December 2005

b) CTIA Test Plan for Hearing Aid Compatibility, Rev 3.1.1, May 2017

## Methods Applied and Interpretation of Parameters:

- NORMx,y,z: Assessed for E-field polarization 9 = 0 for XY sensors and 9 = 90 for Z sensor (f ≤ 900 MHz in TEM-cell; f > 1800 MHz: R22 waveguide).
- NORM(f)x,y,z = NORMx,y,z \* frequency\_response (see Frequency Response Chart).
- DCPx,y,z: DCP are numerical linearization parameters assessed based on the data of power sweep with CW signal (no uncertainty required). DCP does not depend on frequency nor media.
- PAR: PAR is the Peak to Average Ratio that is not calibrated but determined based on the signal characteristics
- Ax,y,z; Bx,y,z; Cx,y,z; Dx,y,z; VRx,y,z: A, B, C, D are numerical linearization parameters assessed based on
  the data of power sweep for specific modulation signal. The parameters do not depend on frequency nor
  media. VR is the maximum calibration range expressed in RMS voltage across the diode.
- Spherical isotropy (3D deviation from isotropy): in a locally homogeneous field realized using an open waveguide setup.
- Sensor Offset: The sensor offset corresponds to the offset of virtual measurement center from the probe tip (on probe axis). No tolerance required.
- Connector Angle: The angle is assessed using the information gained by determining the NORMx (no
  uncertainty required).

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EF3DV3 - SN:4035 January 16, 2019

# DASY/EASY - Parameters of Probe: EF3DV3 - SN:4035

## **Basic Calibration Parameters**

	Sensor X	Sensor Y	Sensor Z	Unc (k=2)
Norm (μV/(V/m) <sup>2</sup> )	0.90	0.74	1.20	± 10.1 %
DCP (mV) <sup>B</sup>	96.8	98.5	95.3	

Calibration results for Frequency Response (30 MHz = 6 GHz)

Frequency MHz	Target E-Field V/m	Measured E-field (En) V/m	Deviation E-normal in %	Measured E-field (Ep) V/m	Deviation E-normal in %	Unc (k=2) %
30	77.3	76.8	-0.6%	77.3	0.1%	± 5.1 %
100	77.3	78.2	1.2%	77.8	0.7%	± 5.1 %
450	77.1	78.2	1.5%	77.8	0.9%	± 5.1 %
600	77.1	77.8	0.9%	77.5	0.5%	± 5.1 %
750	77.3	77.7	0.5%	77.2	-0.1%	± 5.1 %
1800	140.3	136.9	-2.4%	137.2	-2.2%	± 5.1 %
2000	133.0	129.4	-2.8%	129.4	-2.7%	± 5.1 %
2200	124.8	121.5	-2.7%	122.7	-1.7%	± 5.1 %
2500	123.7	120.7	-2.4%	121.9	-1.5%	± 5.1 %
3000	78.8	74.8	-5.0%	76.1	-3.5%	± 5.1 %
3500	256.3	248.1	-3.2%	246.0	-4.0%	± 5.1 %
3700	249.7	239.2	-4.2%	239.0	-4.3%	± 5.1 %
5200	50.7	50.7	-0.1%	51.2	0.9%	± 5.1 %
5500	49.6	48.9	-1.5%	48.7	-1.9%	± 5.1 %
5800	48.9	49.1	0.4%	49.3	0.8%	± 5.1 %

Calibration Results for Modulation Response

UID	Communication System Name		A dB	B dB√μV	С	D dB	VR mV	Max dev.	Unc <sup>±</sup> (k=2)
0	CW	Х	0.0	0.0	1.0	0.00	141.5	+ 3.3 %	± 4.7 %
		Υ	0.0	0.0	1.0		125.6		
		Y	0.0	0.0	1.0		125.1		<u> </u>

The reported uncertainty of measurement is stated as the standard uncertainty of measurement multiplied by the coverage factor k=2, which for a normal distribution corresponds to a coverage probability of approximately 95%.

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B Numerical linearization parameter: uncertainty not required.

E Uncertainty is determined using the max. deviation from linear response applying rectangular distribution and is expressed for the square of the

EF3DV3 - SN:4035 January 16, 2019

# DASY/EASY - Parameters of Probe: EF3DV3 - SN:4035

## **Sensor Frequency Model Parameters**

	Sensor X	Sensor Y	Sensor Z
Frequency Corr. (LF)	0.28	0.21	5.68
Frequency Corr. (HF)	2.82	2.82	2.82

#### **Other Probe Parameters**

Sensor Arrangement	Rectangular
Connector Angle (°)	57.9
Mechanical Surface Detection Mode	enabled
Optical Surface Detection Mode	disabled
Probe Overall Length	335 mm
Probe Body Diameter	12 mm
Tip Length	25 mm
Tip Diameter	4 mm
Probe Tip to Sensor X Calibration Point	1.5 mm
Probe Tip to Sensor Y Calibration Point	1.5 mm
Probe Tip to Sensor Z Calibration Point	1.5 mm

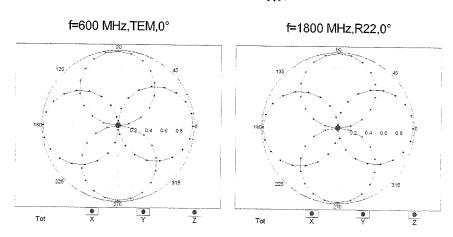
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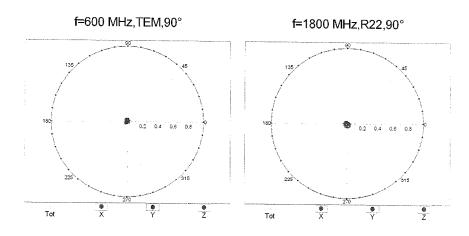
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# Receiving Pattern ( $\phi$ ), $\vartheta = 0^{\circ}$



# Receiving Pattern ( $\phi$ ), $\vartheta$ = 90°



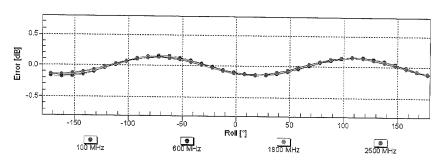
Certificate No: EF3-4035\_Jan19

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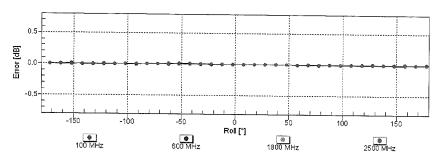
EF3DV3 - SN:4035 January 16, 2019

# Receiving Pattern ( $\phi$ ), $\vartheta = 0^{\circ}$



Uncertainty of Axial Isotropy Assessment: ± 0.5% (k=2)

# Receiving Pattern ( $\phi$ ), $\vartheta = 90^{\circ}$



Uncertainty of Axial Isotropy Assessment: ± 0.5% (k=2)

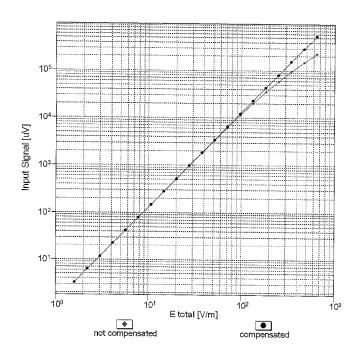
Certificate No: EF3-4035\_Jan19

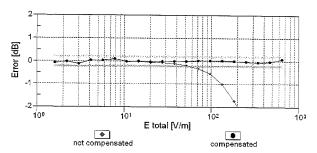
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# Dynamic Range f(E-field) (TEM cell, f = 900 MHz)





Uncertainty of Linearity Assessment: ± 0.6% (k=2)

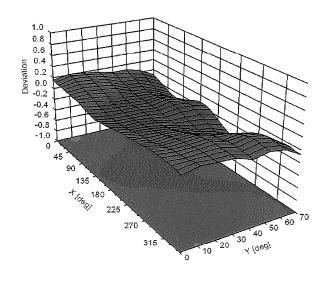
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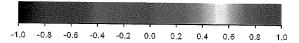
Approved by: FCC ID: A3LSMA102U HAC (RF EMISSIONS) TEST REPORT SAMSUNG Quality Manager DUT Type: Filename: Test Dates: Page 72 of 96 1M1904030051-12-R1.A3L 04/29/2019 - 05/01/2019 Portable Handset

EF3DV3 - SN:4035 January 16, 2019

# **Deviation from Isotropy in Air**

Error (♦, ३), f = 900 MHz





Uncertainty of Spherical Isotropy Assessment:  $\pm 2.6\%$  (k=2)

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# **Calibration Laboratory of**

Schmid & Partner Engineering AG Zeughausstrasse 43, 8004 Zurich, Switzerland





Schweizerischer Kalibrierdienst S Service suisse d'étalonnage C Servizio svizzero di taratura Swiss Calibration Service

Accreditation No.: SCS 0108

Accredited by the Swiss Accreditation Service (SAS) The Swiss Accreditation Service is one of the signatories to the EA Multilateral Agreement for the recognition of calibration certificates

Client

Certificate No: CD835V3-1003\_Feb19

Calibration procedure(s)  QA CAL-20.v7 Calibration Procedure for Validation Sources in air  VIA  April 1912  Calibration date:  February 19, 2019  This calibration certificate documents the traceability to national standards, which realize the physical units of measurements (SI). The measurements and the uncertainties with confidence probability are given on the following pages and are part of the certificate.  All calibrations have been conducted in the closed laboratory facility: environment temperature (22 ± 3)°C and humidity < 70%.  Calibration Equipment used (M&TE critical for calibration)  Primary Standards  ID # Cal Date (Certificate No.) Scheduled Calibration  Power meter NRP  Power sensor NRP-291  SN: 103244  04-Apr-18 (No. 217-02672)02673)  Apr-19  Power sensor NRP-291  SN: 103245  O4-Apr-18 (No. 217-02672)  Apr-19  Reference 20 dB Altenuator  SN: 5047 2 / 06327  04-Apr-18 (No. 217-02683)  Apr-19  Type-N mismatch combination  SN: 5047 2 / 06327  04-Apr-18 (No. 217-02683)  Apr-19  DAE4  SN: 781  D9-Jan-19 (No. DAE4-781_Jan19)  Jan-20  Sceondary Standards  D# Check Date (in house)  Scheduled Check  Check Date (in house check Oct-17)  In house check: Oct-20  In house check: Oct-20	Object	CD835V3 - SN;	1003	
This calibration certificate documents the traceability to national standards, which realize the physical units of measurements (SI). The measurements and the uncertainties with confidence probability are given on the following pages and are part of the certificate.  All calibrations have been conducted in the closed laboratory facility: environment temperature (22 ± 3)°C and humidity < 70%.  Calibration Equipment used (M&TE critical for calibration)  Primary Standards   D # Cal Date (Certificate No.) Scheduled Calibration  Power meter NRP  Power meter NRP   SN: 104778   04-Apr-18 (No. 217-02672)   Apr-19    Power sensor NRP-Z91   SN: 103244   04-Apr-18 (No. 217-02672)   Apr-19    Power sensor NRP-Z91   SN: 103245   04-Apr-18 (No. 217-02672)   Apr-19    Reference 20 dB Attenuator   SN: 5058 (20k)   04-Apr-18 (No. 217-02682)   Apr-19    Type-N mismatch combination   SN: 5047.2 / 06327   04-Apr-18 (No. 217-02683)   Apr-19    Probe EF3DV3   SN: 4013   03-Jan-19 (No. EF3-4013_Jan19)   Jan-20    DAE4   SN: 781   09-Jan-19 (No. DAE4-781_Jan19)   Jan-20    Secondary Standards   ID # Check Date (in house)   Scheduled Check    Power meter Agilent 4419B   SN: GB42420191   09-Oct-09 (in house check Oct-17)   In house check: Oct-20    Power sensor HP E4412A   SN: US38485102   05-Jan-10 (in house check Oct-17)   In house check: Oct-20    Power sensor HP B482A   SN: US37295597   09-Oct-09 (in house check Oct-17)   In house check: Oct-20    Ref generator R&S SMT-06   SN: 383283/011   27-Aug-12 (in house check Oct-17)   In house check: Oct-20    Ref generator R&S SMT-06   SN: 383283/011   27-Aug-12 (in house check Oct-17)   In house check: Oct-20    Ref generator R&S SMT-06   SN: 283283/011   27-Aug-12 (in house check Oct-17)   In house check: Oct-20    Ref generator R&S SMT-06   SN: 283283/011   27-Aug-12 (in house check Oct-17)   In house check: Oct-20    Ref generator R&S SMT-06   SN: 283283/011   27-Aug-12 (in house check Oct-17)   In house check: Oct-20    Ref generator R&S SMT-06   SN: 283283/011   27-Aug-12 (in house ch	Calibration procedure(s)		edure for Validation Sources in a	ir VOA Y11/12
The measurements and the uncertainties with confidence probability are given on the following pages and are part of the certificate.  All calibrations have been conducted in the closed laboratory facility: environment temperature (22 ± 3)°C and humidity < 70%.  Calibration Equipment used (M&TE critical for calibration)  Primary Standards  ID # Cal Date (Certificate No.) Scheduled Calibration  Power meter NRP  Power meter NRP  Power sensor NRP-Z91 SN: 103244 04-Apr-18 (No. 217-02672) Apr-19  Power sensor NRP-Z91 SN: 103245 04-Apr-18 (No. 217-02673) Apr-19  Reference 20 dB Attenuator SN: 5058 (20k) 04-Apr-18 (No. 217-02682) Apr-19  Type-N mismatch combination SN: 5058 (20k) 04-Apr-18 (No. 217-02683) Apr-19  Type-N mismatch combination SN: 5047.2 / 06327 04-Apr-18 (No. 217-02683) Apr-19  Probe EF3DV3 SN: 4013 03-Jan-19 (No. EF3-4013_Jan19) Jan-20  DAE4 SN: 781 09-Jan-19 (No. DAE4-781_Jan19) Jan-20  Secondary Standards  ID # Check Date (in house) Scheduled Check  Power meter Agilent 4419B SN: GB42420191 09-Oct-09 (in house check Oct-17) In house check: Oct-20 Power sensor HP E4412A SN: US38485102 05-Jan-10 (in house check Oct-17) In house check: Oct-20 Reference R&S SMT-06 SN: 3832285/011 27-Aug-12 (in house check Oct-17) In house check: Oct-20 Reference R&S SMT-06 SN: 3832285/011 27-Aug-12 (in house check Oct-17) In house check: Oct-20 Reference R&S SMT-06 SN: 3832285/011 27-Aug-12 (in house check Oct-17) In house check: Oct-20 Reference R&S SMT-06 SN: 3832285/011 27-Aug-12 (in house check Oct-17) In house check: Oct-20 Reference R&S SMT-06 SN: 3832285/011 27-Aug-12 (in house check Oct-17) In house check: Oct-20 Reference R&S SMT-06 SN: 3832285/011 27-Aug-12 (in house check Oct-17) In house check: Oct-20 Reference R&S SMT-06 SN: 3832285/011 27-Aug-12 (in house check Oct-17) In house check: Oct-20 Reference R&S SMT-06 SN: 3832285/011 27-Aug-12 (in house check Oct-17) In house check: Oct-20 Reference R&S SMT-06 SN: 3832285/011 27-Aug-12 (in house check Oct-17) In house check: Oct-20 Reference R&S SMT-06 SN: 3832285/	Calibration date:	February 19, 20	19	
D# Cal Date (Certificate No.)   Scheduled Calibration	All calibrations have been condu	ertainties with confidence p	probability are given on the following pages ar	nd are part of the certificate.
Power meter NRP				
Power sensor NRP-Z91 SN: 103244 04-Apr-18 (No. 217-02672) Apr-19 Power sensor NRP-Z91 SN: 103245 04-Apr-18 (No. 217-02673) Apr-19 Reference 20 dB Attenuator SN: 5058 (20k) 04-Apr-18 (No. 217-02682) Apr-19 Type-N mismatch combination SN: 5047.2 / 06327 04-Apr-18 (No. 217-02683) Apr-19 Probe EF3DV3 SN: 4013 03-Jan-19 (No. EF3-4013_Jan19) Jan-20 DAE4 SN: 781 09-Jan-19 (No. DAE4-781_Jan19) Jan-20  Secondary Standards ID # Check Date (in house) Scheduled Check Power meter Agilent 4419B SN: GB42420191 09-Oct-09 (in house check Oct-17) In house check: Oct-20 Power sensor HP E4412A SN: US38485102 05-Jan-10 (in house check Oct-17) In house check: Oct-20 Power sensor HP 8482A SN: US37295597 09-Oct-09 (in house check Oct-17) In house check: Oct-20 Ref generator R&S SMT-06 SN: 832283/011 27-Aug-12 (in house check Oct-17) In house check: Oct-20 Network Analyzer HP 8358A SN: US41080477 31-Mar-14 (in house check Oct-18) In house check: Oct-19  Name Function Signature  Claudio Leubler Laboratory Technician			·	
Power sensor NRP-291 SN: 103245 04-Apr-18 (No. 217-02672) Apr-19 Reference 20 dB Attenuator SN: 5058 (20k) 04-Apr-18 (No. 217-02682) Apr-19 Type-N mismatch combination SN: 5047.2 / 06327 04-Apr-18 (No. 217-02682) Apr-19 Probe EF3DV3 SN: 4013 03-Jan-19 (No. EF3-4013_Jan19) Jan-20 DAE4 SN: 781 09-Jan-19 (No. DAE4-781_Jan19) Jan-20  Secondary Standards ID # Check Date (in house) Scheduled Check Power meter Agilent 4419B SN: GB42420191 09-Oct-09 (in house check Oct-17) In house check: Oct-20 Power sensor HP E4412A SN: US38485102 05-Jan-10 (in house check Oct-17) In house check: Oct-20 Power sensor HP B482A SN: US37295597 09-Oct-09 (in house check Oct-17) In house check: Oct-20 Ref generator R&S SMT-06 SN: 832283/011 27-Aug-12 (in house check Oct-17) In house check: Oct-20 Retwork Analyzer HP 8358A SN: US41080477 31-Mar-14 (in house check Oct-18) In house check: Oct-19  Name Function Signature  Calibrated by: Claudio Leubler Laboratory Technician				<u>.</u>
Secondary Standards		l l		•
Type-N mismatch combination			, ,	•
SN: 4013   O3-Jan-19 (No. EF3-4013_Jan19)   Jan-20				
SN: 781   O9-Jan-19 (No. DAE4-781_Jan19)   Jan-20			· · · · · · · · · · · · · · · · · · ·	•
Power meter Agilent 4419B Power sensor HP E4412A Power sensor HP E4412A SN: US38485102 SN: US37295597 SN: US41080477 SN: US410	DAE4	1		
Power meter Agilent 4419B Power sensor HP E4412A Power sensor HP E4412A SN: US38485102 SN: US37295597 SN: US41080477 SN: US410	_	ı		
Power sensor HP E4412A Power sensor HP 8482A SN: US38485102 SN: US37295597 SN: US41080477 SN: US			Check Date (in house)	Scheduled Check
Power sensor HP 8482A SR: US37295597 O9-Oct-09 (in house check Oct-17) In house check: Oct-20 In house check: Oct-19 In house check: Oct-20 In house check: Oct-		SN: GB42420191	09-Oct-09 (in house check Oct-17)	In house check: Oct-20
SR generator R&S SMT-06 Network Analyzer HP 8358A SN: 832283/011 SN: US41080477 SN: War-14 (In house check Oct-17) SN: War-14 (In house check Oct-18) Name Function Claudio Leubler Function Laboratory Technician Signature		SN: US38485102	05-Jan-10 (in house check Oct-17)	In house check: Oct-20
Network Analyzer HP 8358A SN: US41080477 31-Mar-14 (In house check Oct-18) In house check: Oct-19  Name Function Signature  Claudio Leubler Laboratory Technician		SN: US37295597	09-Oct-09 (in house check Oct-17)	In house check: Oct-20
Network Analyzer HP 8358A SN: US41080477 31-Mar-14 (in house check Oct-18) In house check: Oct-19  Name Function Signature  Claudio Leubler Laboratory Technician		SN: 832283/011	27-Aug-12 (in house check Oct-17)	
Calibrated by: Claudio Leubler Laboratory Technician	Matwork Applyzor HD 00E0A	SN: US41080477	31-Mar-14 (in house check Oct-18)	
Calibrated by: Claudio Leubler Laboratory Technician	TOWOR Analyzer Fir 6556A	Name	Function	Signature
	WORK Analyzer Fir 6556A	the transport of the first of the contract of	Laboratory Technician	ITV
Approved by: Katja Pokovic Technical Manager	,	Claudio Leubler		(   \( \) ( )
Lelly	,	Claudio Leubler		\
	Calibrated by:		Technical Manager	

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## Calibration Laboratory of Schmid & Partner

**Engineering AG** Zeughausstrasse 43, 8004 Zurich, Switzerland





Schweizerischer Kalibrierdienst Service suisse d'étalonnage Servizio svizzero di taratura Swiss Calibration Service

Accreditation No.: SCS 0108

Accredited by the Swiss Accreditation Service (SAS) The Swiss Accreditation Service is one of the signatories to the EA Multilateral Agreement for the recognition of calibration certificates

#### References

ANSI-C63.19-2011 [1] American National Standard, Methods of Measurement of Compatibility between Wireless Communications Devices and Hearing Aids,

## Methods Applied and Interpretation of Parameters:

- Coordinate System: y-axis is in the direction of the dipole arms. z-axis is from the basis of the antenna (mounted on the table) towards its feed point between the two dipole arms. x-axis is normal to the other axes. In coincidence with the standards [1], the measurement planes (probe sensor center) are selected to be at a distance of 15 mm above the top metal edge of the dipole arms.
- Measurement Conditions: Further details are available from the hardcopies at the end of the certificate. All figures stated in the certificate are valid at the frequency indicated. The forward power to the dipole connector is set with a calibrated power meter connected and monitored with an auxiliary power meter connected to a directional coupler. While the dipole under test is connected, the forward power is adjusted to the same level.
- Antenna Positioning: The dipole is mounted on a HAC Test Arch phantom using the matching dipole positioner with the arms horizontal and the feeding cable coming from the floor. The measurements are performed in a shielded room with absorbers around the setup to reduce the reflections. It is verified before the mounting of the dipole under the Test Arch phantom, that its arms are perfectly in a line. It is installed on the HAC dipole positioner with its arms parallel below the dielectric reference wire and able to move elastically in vertical direction without changing its relative position to the top center of the Test Arch phantom. The vertical distance to the probe is adjusted after dipole mounting with a DASY5 Surface Check job. Before the measurement, the distance between phantom surface and probe tip is verified. The proper measurement distance is selected by choosing the matching section of the HAC Test Arch phantom with the proper device reference point (upper surface of the dipole) and the matching grid reference point (tip of the probe) considering the probe sensor offset. The vertical distance to the probe is essential for the
- Feed Point Impedance and Return Loss: These parameters are measured using a HP 8753E Vector Network Analyzer. The impedance is specified at the SMA connector of the dipole. The influence of reflections was eliminating by applying the averaging function while moving the dipole in the air, at least 70cm away from any
- E-field distribution: E field is measured in the x-y-plane with an isotropic ER3D-field probe with 100 mW forward power to the antenna feed point. In accordance with [1], the scan area is 20mm wide, its length exceeds the dipole arm length (180 or 90mm). The sensor center is 15 mm (in z) above the metal top of the dipole arms. Two 3D maxima are available near the end of the dipole arms. Assuming the dipole arms are perfectly in one line, the average of these two maxima (in subgrid 2 and subgrid 8) is determined to compensate for any non-parallelity to the measurement plane as well as the sensor displacement. The E-field value stated as calibration value represents the maximum of the interpolated 3D-E-field, in the plane above the dipole surface.

The reported uncertainty of measurement is stated as the standard uncertainty of measurement multiplied by the
coverage factor k=2, which for a normal distribution corresponds to a coverage probability of approximately 95%.

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## **Measurement Conditions**

DASY system configuration, as far as not given on page 1.

DASY Version	DASY5	V52.10.2
Phantom	HAC Test Arch	
Distance Dipole Top - Probe Center	15 mm	
Scan resolution	dx, dy = 5 mm	
Frequency	835 MHz ± 1 MHz	
Input power drift	< 0.05 dB	

### Maximum Field values at 835 MHz

E-field 15 mm above dipole surface	condition	Interpolated maximum
Maximum measured above high end	100 mW input power	105.2 V/m = 40.44 dBV/m
Maximum measured above low end	100 mW input power	105.1 V/m = 40.43 dBV/m
Averaged maximum above arm	100 mW input power	105.2 V/m ± 12.8 % (k=2)

## Appendix (Additional assessments outside the scope of SCS 0108)

### **Antenna Parameters**

Frequency	Return Loss	Impedance
800 MHz	17.6 dB	40.4 Ω - 7.2 jΩ
835 MHz	25.8 dB	52.2 Ω + 4.7 jΩ
880 MHz	16.9 dB	62.1 Ω - 10.5 jΩ
900 MHz	16.9 dB	52.2 Ω - 14.6  Ω
945 MHz	21.6 dB	51.8 Ω + 8.3 jΩ

## 3.2 Antenna Design and Handling

The calibration dipole has a symmetric geometry with a built-in two stub matching network, which leads to the enhanced bandwidth.

The dipole is built of standard semirigid coaxial cable. The internal matching line is open ended. The antenna is therefore open for DC signals.

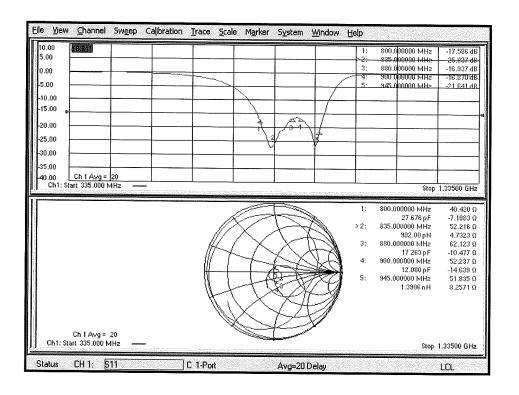
Do not apply force to dipole arms, as they are liable to bend. The soldered connections near the feedpoint may be damaged. After excessive mechanical stress or overheating, check the impedance characteristics to ensure that the internal matching network is not affected.

After long term use with 40W radiated power, only a slight warming of the dipole near the feedpoint can be measured.

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## **Impedance Measurement Plot**



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### **DASY5 E-field Result**

Date: 19.02.2019

Test Laboratory: SPEAG Lab2

## DUT: HAC-Dipole 835 MHz; Type: CD835V3; Serial: CD835V3 - SN: $1003\,$

Communication System: UID 0 - CW; Frequency: 835 MHz Medium parameters used:  $\sigma = 0$  S/m,  $\epsilon_r = 1$ ;  $\rho = 0$  kg/m<sup>3</sup> Phantom section: RF Section

Measurement Standard: DASY5 (IEEE/IEC/ANSI C63.19-2011)

## DASY52 Configuration:

- Probe: EF3DV3 SN4013; ConvF(1, 1, 1) @ 835 MHz; Calibrated: 03.01.2019
- Sensor-Surface: (Fix Surface)
- Electronics: DAE4 Sn781; Calibrated: 09.01.2019
- Phantom: HAC Test Arch with AMCC; Type: SD HAC P01 BA; Serial: 1070
- DASY52 52.10.2(1495); SEMCAD X 14.6.12(7450)

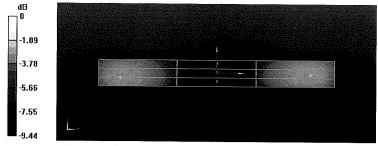
## Dipole E-Field measurement @ 835MHz/E-Scan - 835MHz d=15mm/Hearing Aid Compatibility Test (41x361x1):

Interpolated grid: dx=0.5000 mm, dy=0.5000 mm Device Reference Point: 0, 0, -6.3 mm Reference Value = 127.3 V/m; Power Drift = 0.04 dB Applied MIF = 0.00 dBRF audio interference level = 40.44 dBV/m

Emission category: M3

#### MIF scaled E-field

Grid 1 M4	Grid 2 <b>M3</b>	Grid 3 M3
39.75 dBV/m	40.43 dBV/m	40.43 dBV/m
Grid 4 <b>M4</b>	Grid 5 M4	Grid 6 M4
35.35 dBV/m	35.75 dBV/m	35.73 dBV/m
Grid 7 <b>M3</b>	Grid 8 <b>M3</b>	Grid 9 <b>M3</b>
40.15 dBV/m	40.44 dBV/m	40.36 dBV/m



0 dB = 105.2 V/m = 40.44 dBV/m

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#### Calibration Laboratory of Schmid & Partner Engineering AG Zeughausstrasse 43, 8004 Zurich, Switzerland





Schweizerischer Kalibrierdienst S Service suisse d'étalonnage C Servizio svizzero di taratura Swiss Calibration Service

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Accreditation No.: SCS 0108

Client

PC Test

Certificate No: CD1880V3-1137 Feb19

Object	CD1880V3 - SN	: 1137		
Calibration procedure(s)	QA CAL-20.v7 Calibration Proc	edure for Validation Sources in a	ir	/0: 3/19/2
Calibration date:	February 19, 20	19		
The measurements and the unce	ertainties with confidence p	ional standards, which realize the physical ur probability are given on the following pages ar rry facility: environment temperature $(22 \pm 3)^{\circ}$	nd are part of the certificate.	
Primary Standards	ID#	Col Data (Continue No. )		
Power meter NRP	SN: 104778	Cal Date (Certificate No.) 04-Apr-18 (No. 217-02672/02673)	Scheduled Calibration	
Power sensor NRP-Z91	SN: 103244	04-Apr-18 (No. 217-02672)	Apr-19	
Power sensor NRP-Z91	SN: 103245	04-Apr-18 (No. 217-02673)	Apr-19	
Reference 20 dB Attenuator	SN: 5058 (20k)	04-Apr-18 (No. 217-02673)	Apr-19	
Type-N mismatch combination	SN: 5047.2 / 06327		Apr-19	
Probe EF3DV3	SN: 4013	04-Apr-18 (No. 217-02683)	Apr-19	
DAE4	SN: 781	03-Jan-19 (No. EF3-4013_Jan19) 09-Jan-19 (No. DAE4-781_Jan19)	Jan-20 Jan-20	
Secondary Standards	ID #	Check Date (in house)	Scheduled Check	
Power meter Agilent 4419B	SN: GB42420191	09-Oct-09 (in house check Oct-17)	In house check: Oct-20	
Power sensor HP E4412A	SN: US38485102	05-Jan-10 (in house check Oct-17)	In house check: Oct-20	
Power sensor HP 8482A	SN: US37295597	09-Oct-09 (in house check Oct-17)	In house check; Oct-20	
RF generator R&S SMT-06	SN: 832283/011	27-Aug-12 (in house check Oct-17)	In house check; Oct-20	
Network Analyzer HP 8358A	SN: US41080477	31-Mar-14 (in house check Oct-18)	In house check: Oct-19	
	Name	Function	Signature	
Calibrated by:	Claudio Leubler	Laboratory Technician		
pproved by:	Kalja Pokovic	Technical Manager	AU L	

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### Calibration Laboratory of

Schmid & Partner
Engineering AG
Zeughausstrasse 43, 8004 Zurich, Switzerland





S Schweizerischer Kalibrierdienst
C Service suisse d'étalonnage
Servizio svizzero di taratura
Swiss Calibration Service

Accreditation No.: SCS 0108

Accredited by the Swiss Accreditation Service (SAS)

The Swiss Accreditation Service is one of the signatories to the EA

Multilateral Agreement for the recognition of calibration certificates

#### References

[1] ANSI-C63.19-2011

American National Standard, Methods of Measurement of Compatibility between Wireless Communications Devices and Hearing Aids.

### Methods Applied and Interpretation of Parameters:

- Coordinate System: y-axis is in the direction of the dipole arms. z-axis is from the basis of the antenna
  (mounted on the table) towards its feed point between the two dipole arms. x-axis is normal to the other axes.
  In coincidence with the standards [1], the measurement planes (probe sensor center) are selected to be at a
  distance of 15 mm above the top metal edge of the dipole arms.
- Measurement Conditions: Further details are available from the hardcopies at the end of the certificate. All
  figures stated in the certificate are valid at the frequency indicated. The forward power to the dipole connector
  is set with a calibrated power meter connected and monitored with an auxiliary power meter connected to a
  directional coupler. While the dipole under test is connected, the forward power is adjusted to the same level.
- Antenna Positioning: The dipole is mounted on a HAC Test Arch phantom using the matching dipole positioner with the arms horizontal and the feeding cable coming from the floor. The measurements are performed in a shielded room with absorbers around the setup to reduce the reflections. It is verified before the mounting of the dipole under the Test Arch phantom, that its arms are perfectly in a line. It is installed on the HAC dipole positioner with its arms parallel below the dielectric reference wire and able to move elastically in vertical direction without changing its relative position to the top center of the Test Arch phantom. The vertical distance to the probe is adjusted after dipole mounting with a DASY5 Surface Check job. Before the measurement, the distance between phantom surface and probe tip is verified. The proper measurement distance is selected by choosing the matching section of the HAC Test Arch phantom with the proper device reference point (upper surface of the dipole) and the matching grid reference point (tip of the probe) considering the probe sensor offset. The vertical distance to the probe is essential for the accuracy.
- Feed Point Impedance and Return Loss: These parameters are measured using a HP 8753E Vector Network
  Analyzer. The impedance is specified at the SMA connector of the dipole. The influence of reflections was
  eliminating by applying the averaging function while moving the dipole in the air, at least 70cm away from any
  obstacles.
- E-field distribution: E field is measured in the x-y-plane with an isotropic ER3D-field probe with 100 mW forward power to the antenna feed point. In accordance with [1], the scan area is 20mm wide, its length exceeds the dipole arm length (180 or 90mm). The sensor center is 15 mm (in z) above the metal top of the dipole arms. Two 3D maxima are available near the end of the dipole arms. Assuming the dipole arms are perfectly in one line, the average of these two maxima (in subgrid 2 and subgrid 8) is determined to compensate for any non-parallelity to the measurement plane as well as the sensor displacement. The E-field value stated as calibration value represents the maximum of the interpolated 3D-E-field, in the plane above the dipole surface.

The reported uncertainty of measurement is stated as the standard uncertainty of measurement mu	tiplied by the
coverage factor k=2, which for a normal distribution corresponds to a coverage probability of approx	imately 95%.

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### **Measurement Conditions**

DASY system configuration, as far as not given on page 1.

DASY Version	DASY5	V52.10.2
Phantom	HAC Test Arch	
Distance Dipole Top - Probe Center	15 mm	
Scan resolution	dx, dy = 5 mm	
Frequency	1730 MHz ± 1 MHz 1880 MHz ± 1 MHz	
Input power drift	< 0.05 dB	

#### Maximum Field values at 1730 MHz

E-field 15 mm above dipole surface	condition	Interpolated maximum	
Maximum measured above high end	100 mW input power	95.0 V/m = 39.55 dBV/m	
Maximum measured above low end	100 mW input power	94.9 V/m = 39.55 dBV/m	
Averaged maximum above arm	100 mW input power	95.0 V/m ± 12.8 % (k=2)	

### Maximum Field values at 1880 MHz

E-field 15 mm above dipole surface	condition	Interpolated maximum	
Maximum measured above high end	100 mW input power	88.9 V/m = 38.98 dBV/m	
Maximum measured above low end	100 mW input power	86.6 V/m = 38.75 dBV/m	
Averaged maximum above arm	100 mW input power	87.8 V/m ± 12.8 % (k=2)	

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## Appendix (Additional assessments outside the scope of SCS 0108)

#### **Antenna Parameters**

#### **Nominal Frequencies**

Frequency	Return Loss	Impedance
1730 MHz	22.5 dB	54.4 Ω + 6.5 jΩ
1880 MHz	21.1 dB	55.9 Ω + 7.2 jΩ
1900 MHz	21.0 dB	59.0 Ω + 3.6 jΩ
1950 MHz	27.3 dB	53.0 Ω - 3.3 jΩ
2000 MHz	20.3 dB	$42.4 \Omega + 4.8 j\Omega$

## 3.2 Antenna Design and Handling

The calibration dipole has a symmetric geometry with a built-in two stub matching network, which leads to the enhanced bandwidth.

The dipole is built of standard semirigid coaxial cable. The internal matching line is open ended. The antenna is therefore open for DC signals.

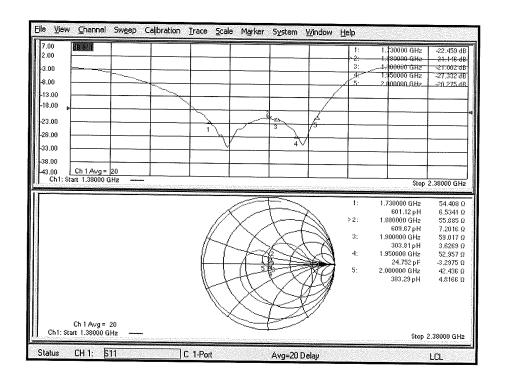
Do not apply force to dipole arms, as they are liable to bend. The soldered connections near the feedpoint may be damaged. After excessive mechanical stress or overheating, check the impedance characteristics to ensure that the internal matching network is not affected.

After long term use with 40W radiated power, only a slight warming of the dipole near the feedpoint can be measured.

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## **Impedance Measurement Plot**



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### **DASY5 E-field Result**

Date: 19.02.2019

Test Laboratory: SPEAG Lab2

## DUT: HAC Dipole 1880 MHz; Type: CD1880V3; Serial: CD1880V3 - SN: 1137

Communication System: UID 0 - CW; Frequency: 1880 MHz, Frequency: 1730 MHz

Medium parameters used:  $\sigma=0$  S/m,  $\epsilon_r=1;\, \rho=0$  kg/m  $^3$ 

Phantom section: RF Section

Measurement Standard: DASY5 (IEEE/IEC/ANSI C63.19-2011)

#### DASY52 Configuration:

- Probe: EF3DV3 SN4013; ConvF(1, 1, 1) @ 1880 MHz, ConvF(1, 1, 1) @ 1730 MHz; Calibrated: 03.01.2019
- Sensor-Surface: (Fix Surface)
- Electronics: DAE4 Sn781; Calibrated: 09.01.2019
- Phantom: HAC Test Arch with AMCC; Type: SD HAC P01 BA; Serial: 1070
- DASY52 52.10.2(1495); SEMCAD X 14.6.12(7450)

## Dipole E-Field measurement @ 1880MHz/E-Scan - 1880MHz d=15mm/Hearing Aid Compatibility Test (41x181x1):

Interpolated grid: dx=0.5000 mm, dy=0.5000 mm Device Reference Point: 0, 0, -6.3 mm Reference Value = 151.5 V/m; Power Drift = 0.02 dB Applied MIF = 0.00 dBRF audio interference level = 38.98 dBV/m Emission category: M2

#### MIF scaled E-field

Grid 1 <b>M2</b>	Grid 2 <b>M2</b>	Grid 3 M2
38.55 dBV/m	38.98 dBV/m	38.93 dBV/m
Grid 4 M2	Grid 5 M2	Grid 6 M2
35.71 dBV/m	35.97 dBV/m	35.96 dBV/m
Grid 7 <b>M2</b>	Grid 8 <b>M2</b>	Grid 9 <b>M2</b>
38.31 dBV/m	38.75 dBV/m	38.73 dBV/m

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## Dipole E-Field measurement @ 1880MHz /E-Scan - 1730MHz d=15mm/Hearing Aid Compatibility Test (41x181x1):

Interpolated grid: dx=0.5000 mm, dy=0.5000 mm

Device Reference Point: 0, 0, -6.3 mm

Reference Value = 165.0 V/m; Power Drift = 0.03 dB

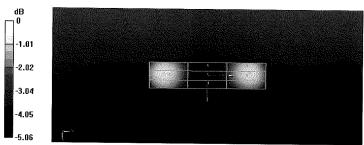
Applied MIF = 0.00 dB

RF audio interference level = 39.55 dBV/m

Emission category: M2

MIF scaled E-field

Grid 1 M2	Grid 2 <b>M2</b>	Grid 3 <b>M2</b>
39.09 dBV/m	39.55 dBV/m	39.51 dBV/m
Grid 4 M2	Grid 5 M2	Grid 6 <b>M2</b>
36.57 dBV/m	36.95 dBV/m	36.95 dBV/m
Grid 7 M2	Grid 8 <b>M2</b>	Grid 9 <b>M2</b>
39.05 dBV/m	39.55 dBV/m	39.53 dBV/m



0 dB = 88.87 V/m = 38.98 dBV/m

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#### Calibration Laboratory of Schmid & Partner Engineering AG

Engineering AG Zeughausstrasse 43, 8004 Zurich, Switzerland





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Accreditation No.: SCS 0108

Client

PC Test

Certificate No: CD2600V3-1012\_Feb19

Object	CD2600V3 - SN	: 1012	
Calibration procedure(s)	QA CAL-20.v7 Calibration Proc	edure for Validation Sources in a	ir 🗸 🗸
			אונ
Calibration date:	February 19, 20	19	
The measurements and the unce	ertainties with confidence p	ional standards, which realize the physical un probability are given on the following pages are ry facility: environment temperature $(22 \pm 3)^{\circ}$ 0	nd are part of the certificate.
Primary Standards	ID#	Cal Date (Certificate No.)	Cabadidad Oatthauttan
Power meter NRP	SN: 104778	04-Apr-18 (No. 217-02672/02673)	Scheduled Calibration
ower sensor NRP-Z91	SN: 103244	04-Apr-18 (No. 217-02672)	Apr-19 Apr-19
ower sensor NRP-Z91	SN: 103245	04-Apr-18 (No. 217-02673)	Apr-19 Apr-19
Reference 20 dB Attenuator	SN: 5058 (20k)	04-Apr-18 (No. 217-02682)	•
ype-N mismatch combination	SN: 5047.2 / 06327	04-Apr-18 (No. 217-02683)	Apr-19
robe EF3DV3	SN: 4013	03-Jan-19 (No. EF3-4013_Jan19)	Apr-19 Jan-20
DAE4	SN: 781	09-Jan-19 (No. DAE4-781_Jan19)	Jan-20 Jan-20
Secondary Standards	1D #	Check Date (in house)	Calculated Observa
ower meter Agilent 4419B	SN: GB42420191	09-Oct-09 (in house check Oct-17)	Scheduled Check
ower sensor HP E4412A	SN: US38485102	05-Jan-10 (in house check Oct-17)	In house check: Oct-20 In house check; Oct-20
ower sensor HP 8482A	SN: US37295597	09-Oct-09 (in house check Oct-17)	In house check; Oct-20
RF generator R&S SMT-06	SN: 832283/011	27-Aug-12 (in house check Oct-17)	In house check: Oct-20
letwork Analyzer HP 8358A	SN: US41080477	31-Mar-14 (in house check Oct-18)	In house check: Oct-19
No Die control de	Name	Function	Signature
alibrated by:	Claudio Leubler	Laboratory Technician	VA
approved by:	Katja Pokovic	Technical Manager	alls

Certificate No: CD2600V3-1012\_Feb19

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## Calibration Laboratory of Schmid & Partner

Engineering AG Zeughausstrasse 43, 8004 Zurich, Switzerland





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#### References

1] ANSI-C63.19-2011

American National Standard, Methods of Measurement of Compatibility between Wireless Communications Devices and Hearing Aids.

## Methods Applied and Interpretation of Parameters:

- Coordinate System: y-axis is in the direction of the dipole arms. z-axis is from the basis of the antenna
  (mounted on the table) towards its feed point between the two dipole arms. x-axis is normal to the other axes.
  In coincidence with the standards [1], the measurement planes (probe sensor center) are selected to be at a
  distance of 15 mm above the top metal edge of the dipole arms.
- Measurement Conditions: Further details are available from the hardcopies at the end of the certificate. All
  figures stated in the certificate are valid at the frequency indicated. The forward power to the dipole connector
  is set with a calibrated power meter connected and monitored with an auxiliary power meter connected to a
  directional coupler. While the dipole under test is connected, the forward power is adjusted to the same level.
- Antenna Positioning: The dipole is mounted on a HAC Test Arch phantom using the matching dipole positioner with the arms horizontal and the feeding cable coming from the floor. The measurements are performed in a shielded room with absorbers around the setup to reduce the reflections. It is verified before the mounting of the dipole under the Test Arch phantom, that its arms are perfectly in a line. It is installed on the HAC dipole positioner with its arms parallel below the dielectric reference wire and able to move elastically in vertical direction without changing its relative position to the top center of the Test Arch phantom. The vertical distance to the probe is adjusted after dipole mounting with a DASY5 Surface Check job. Before the measurement, the distance between phantom surface and probe tip is verified. The proper measurement distance is selected by choosing the matching section of the HAC Test Arch phantom with the proper device reference point (upper surface of the dipole) and the matching grid reference point (tip of the probe) considering the probe sensor offset. The vertical distance to the probe is essential for the accuracy.
- Feed Point Impedance and Return Loss: These parameters are measured using a HP 8753E Vector Network Analyzer. The impedance is specified at the SMA connector of the dipole. The influence of reflections was eliminating by applying the averaging function while moving the dipole in the air, at least 70cm away from any obstacles.
- E-field distribution: E field is measured in the x-y-plane with an isotropic ER3D-field probe with 100 mW forward power to the antenna feed point. In accordance with [1], the scan area is 20mm wide, its length exceeds the dipole arm length (180 or 90mm). The sensor center is 15 mm (in z) above the metal top of the dipole arms. Two 3D maxima are available near the end of the dipole arms. Assuming the dipole arms are perfectly in one line, the average of these two maxima (in subgrid 2 and subgrid 8) is determined to compensate for any non-parallelity to the measurement plane as well as the sensor displacement. The E-field value stated as calibration value represents the maximum of the interpolated 3D-E-field, in the plane above the dipole surface.

The reported uncertainty of measurement is stated as the standard uncertainty of measurement multiplied by the	,
coverage factor k=2, which for a normal distribution corresponds to a coverage probability of approximately 95%.	

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## **Measurement Conditions**

DASY system configuration, as far as not given on page 1.

DASY Version	DASY5	V52.10.2
Phantom	HAC Test Arch	
Distance Dipole Top - Probe Center	15 mm	
Scan resolution	dx, dy = 5 mm	
Frequency	2600 MHz ± 1 MHz	
Input power drift	< 0.05 dB	

#### Maximum Field values at 2600 MHz

E-field 15 mm above dipole surface	condition	Interpolated maximum	
Maximum measured above high end	100 mW input power	85.6 V/m = 38.65 dBV/m	
Maximum measured above low end	100 mW input power	84.7 V/m = 38.56 dBV/m	
Averaged maximum above arm	100 mW input power	85.2 V/m ± 12.8 % (k=2)	

## Appendix (Additional assessments outside the scope of SCS 0108)

## **Antenna Parameters**

Frequency	Return Loss	Impedance	
2450 MHz	20.5 dB	42.7 Ω - 4.8 jΩ	
2550 MHz	32.1 dB	48.9 Ω + 2.2 jΩ	
2600 MHz	39.6 dB	50.3 Ω + 1.0 jΩ	
2650 MHz	30.4 dB	$53.0 \Omega + 0.9 j\Omega$	
2750 MHz	20.9 dB	48.9 Ω - 8.9 ϳΩ	

## 3.2 Antenna Design and Handling

The calibration dipole has a symmetric geometry with a built-in two stub matching network, which leads to the enhanced bandwidth.

The dipole is built of standard semirigid coaxial cable. The internal matching line is open ended. The antenna is therefore open for DC signals.

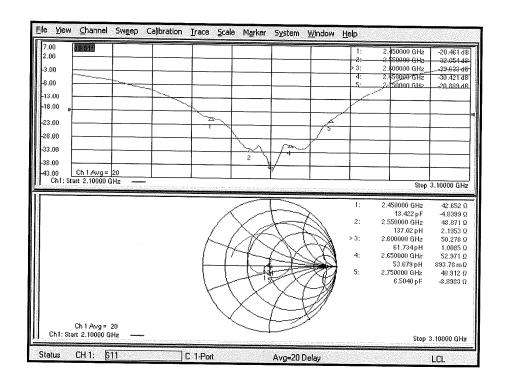
Do not apply force to dipole arms, as they are liable to bend. The soldered connections near the feedpoint may be damaged. After excessive mechanical stress or overheating, check the impedance characteristics to ensure that the internal matching network is not affected.

After long term use with 40W radiated power, only a slight warming of the dipole near the feedpoint can be measured.

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## **Impedance Measurement Plot**



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### **DASY5 E-field Result**

Date: 19.02.2019

Test Laboratory: SPEAG Lab2

## DUT: HAC Dipole 2600 MHz; Type: CD2600V3; Serial: CD2600V3 - SN: 1012

Communication System: UID 0 - CW; Frequency: 2600 MHz Medium parameters used:  $\sigma = 0$  S/m,  $\epsilon_r = 1$ ;  $\rho = 0$  kg/m<sup>3</sup>

Phantom section: RF Section

Measurement Standard: DASY5 (IEEE/IEC/ANSI C63.19-2011)

#### DASY52 Configuration:

- Probe: EF3DV3 SN4013; ConvF(1, 1, 1) @ 2600 MHz; Calibrated: 03.01.2019
- Sensor-Surface: (Fix Surface)
- Electronics: DAE4 Sn781; Calibrated: 09.01.2019
- Phantom: HAC Test Arch with AMCC; Type: SD HAC P01 BA; Serial: 1070
- DASY52 52.10.2(1495); SEMCAD X 14.6.12(7450)

# Dipole E-Field measurement @ 2600MHz - with/E-Scan - 2600MHz d=15mm/Hearing Aid Compatibility Test (41x181x1):

Interpolated grid: dx=0.5000 mm, dy=0.5000 mm

Device Reference Point: 0, 0, -6.3 mm

Reference Value = 62.82 V/m; Power Drift = -0.01 dB

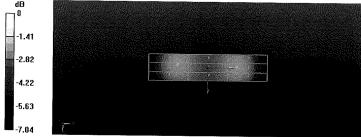
Applied MIF = 0.00 dB

RF audio interference level = 38.65 dBV/m

Emission category: M2

#### MIF scaled E-field

Grid 1 M2	Grid 2 <b>M2</b>	Grid 3 <b>M2</b>
38.09 dBV/m	38.56 dBV/m	38.54 dBV/m
Grid 4 <b>M2</b>	Grid 5 <b>M2</b>	Grid 6 M2
37.82 dBV/m	38.06 dBV/m	38.02 dBV/m
Grid 7 <b>M2</b>	Grid 8 <b>M2</b>	Grid 9 <b>M2</b>
38.36 dBV/m	38.65 dBV/m	38.56 dBV/m



0 dB = 85.60 V/m = 38.65 dBV/m

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#### CONCLUSION 16.

The measurements taken in accordance with the procedures provided in the CTIA Test Plan for Hearing Aid Compatibility Rev 3.1.1, May 2017, indicate that the wireless communications device complies with the HAC limits specified in accordance with the ANSI C63.19 Standard and FCC WT Docket No. 01-309 RM-8658. Precise laboratory measures were taken to assure repeatability of the tests. The tested device complies with the requirements in respect to all parameters specific to the test. The test results and statements relate only to the item(s) tested.

Please note that the M-rating for this equipment only represents the field interference possible against a hypothetical and typical hearing aid. The measurement system and techniques presented in this evaluation are proposed in the ANSI standard as a means of best approximating wireless device compatibility with a hearing-aid. The literature is under continual re-construction.

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